

- DataRace -

Fully Integrated Dual-Polarized Antenna Array with Ultra-Wideband Single-Chip CMOS Receiver

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TUHH

Technische Universität Hamburg



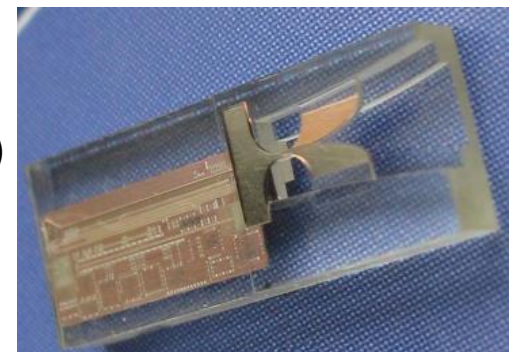
Outline

1. Introduction
2. SPP 1655 – Project Results
3. SPP 1655/2 – Objectives
4. Conclusions and Outlook



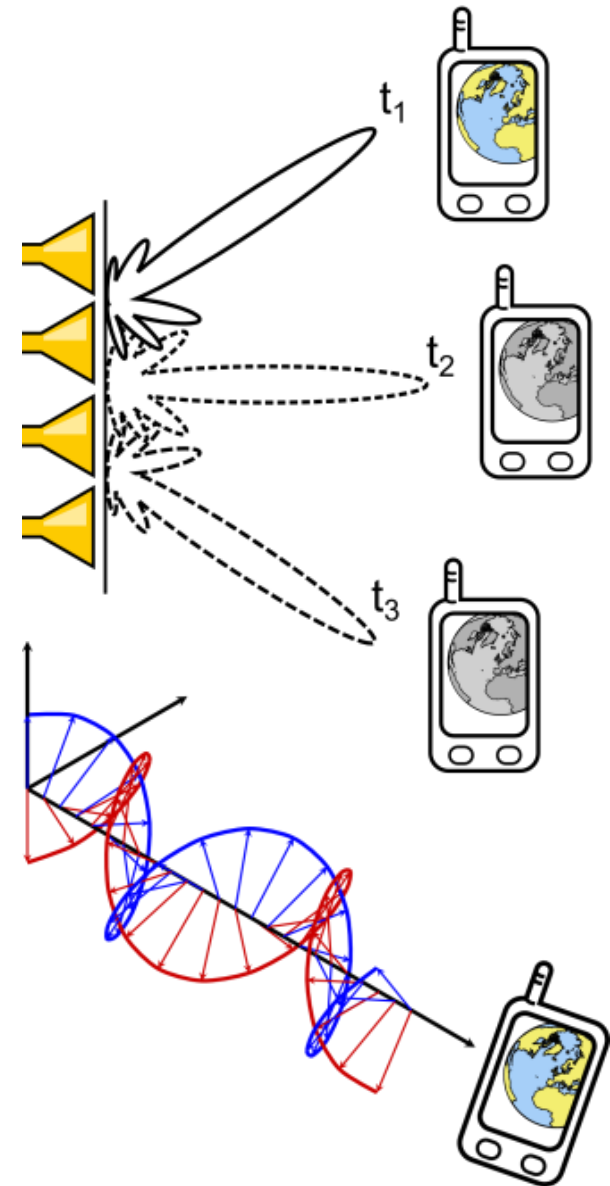
Enabling Technologies for 100 Gb/s

- Low-cost system-in-package
 - Beam-forming system
 - 3D polymer-integrated antenna array
 - Single-chip CMOS transceiver
- Targeting mass-market applications
 - Office-space short-range link (up to 1 m)
 - Video-streaming in airport departure lounges
- Take advantage of entire W-band (75-110 GHz)
 - High relative bandwidth
 - Moderate modulation complexity (moderate SNR)



Array-based Communication Systems

- Arrays for
 - Free space power combining
 - System scalability
 - 2D Phased arrays / beam steering
- Circular polarization
 - Antenna alignment uncritical
- Dual polarization
 - Double data rate
 - Relaxed link budget requirements



Low-Cost Technologies I

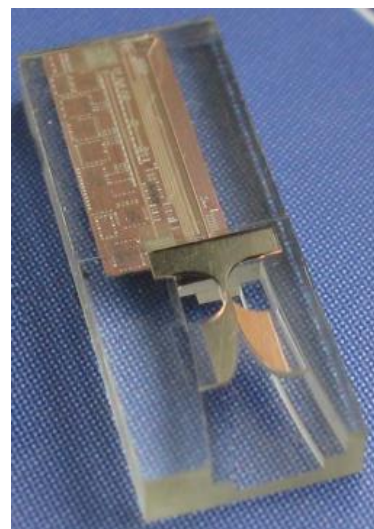
- Polymer process:
 - Vertical growth by polymer deposition and UV-curing
 - Inclined metalized walls
 - Fine resolution (μm scale)
 - Reliable interconnects

- Antenna-in-package
 - Small chip area even for arrays
 - Improved performance
 - Moderate area consumption
 - Wideband system-in-package up to W-band

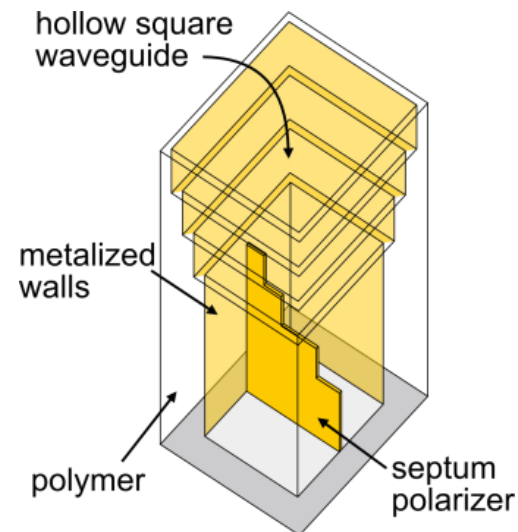


Antenna packaging:

- CM: Conventional module
- AiP: Antenna-in-package
- AoC: Antenna-on-chip

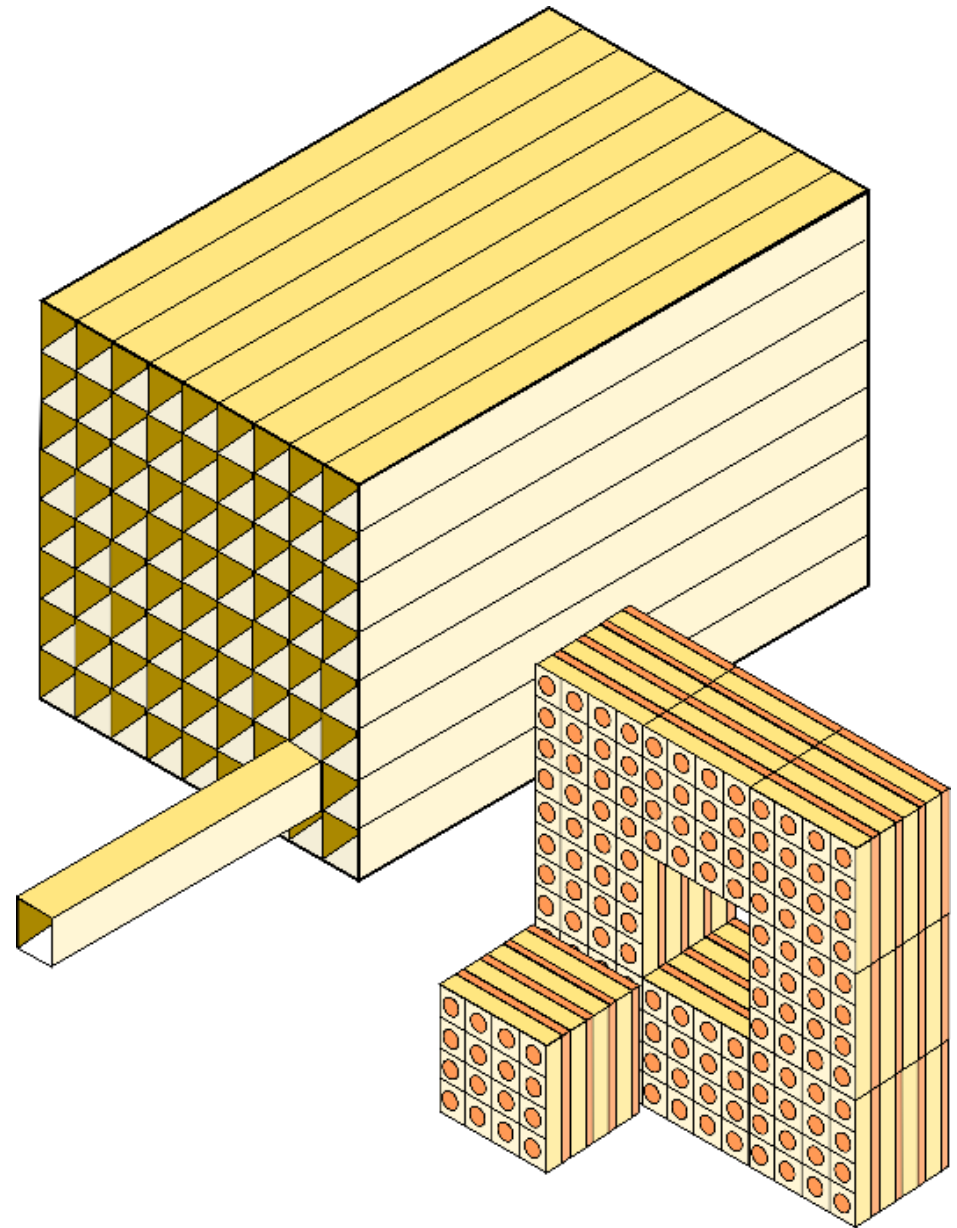


[Tripodi et al.]



Arrays: Brick vs. Tile

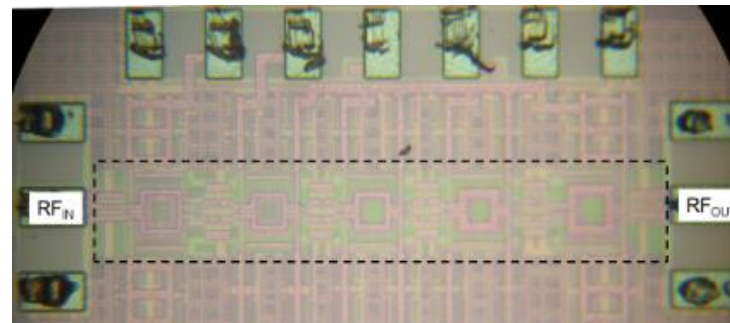
- Brick
 - Simple RF interconnects
 - Scalable to high frequencies
 - Compatible with waveguide
- Tile
 - Layered arrangement
 - Multi-layer PCB process
 - Low thickness



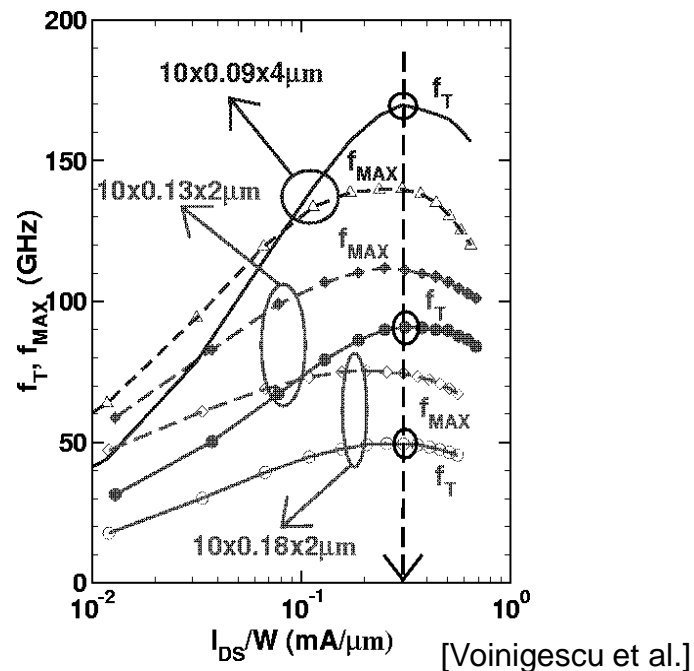
Low-Cost Technologies II

- CMOS technology
 - Highest integration density
 - Mixed signal SoC
 - High reliability
 - Cheap mass production

- CMOS gate length downscaling leads to
 - Increasing f_T/f_{max}
 - Lower current consumption
 - Downscaling driven by digital computing
 - Highest integration density
 - Cheap mass production

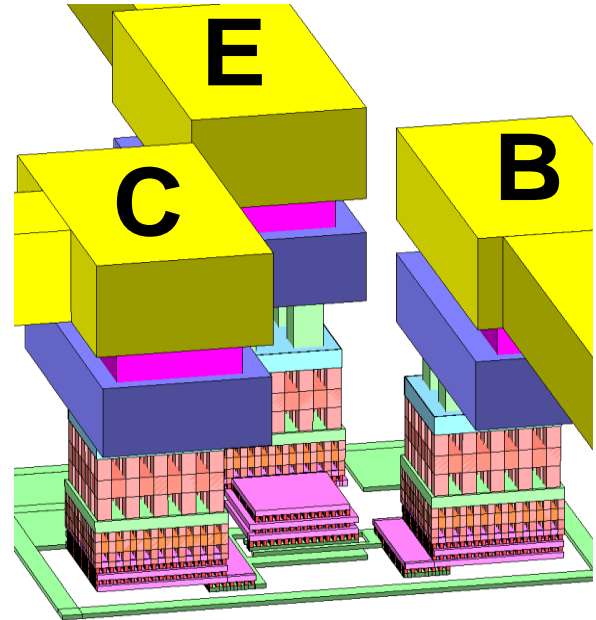
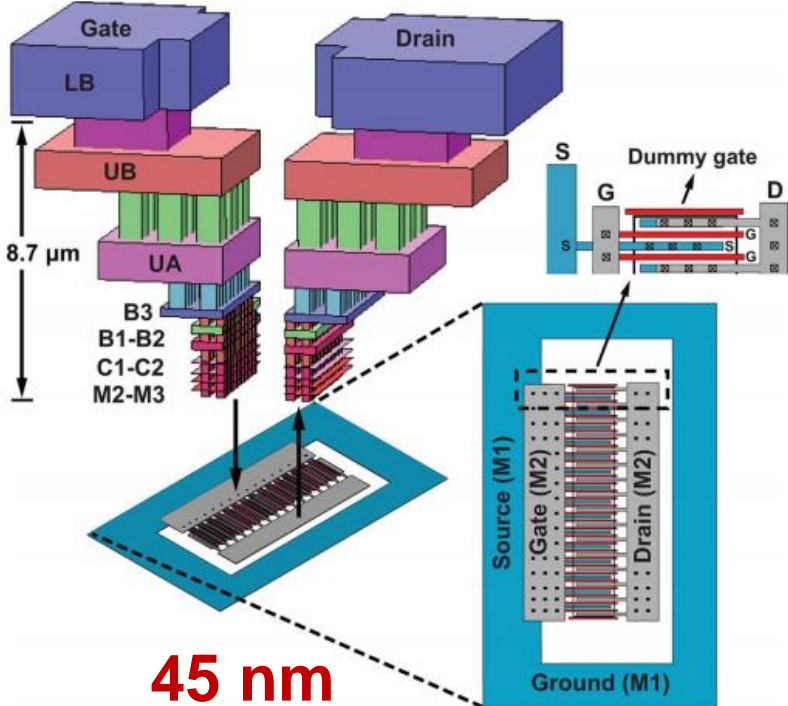


60 GHz CMOS PA with 0.27 mm² chip area



Low-Cost Technologies III

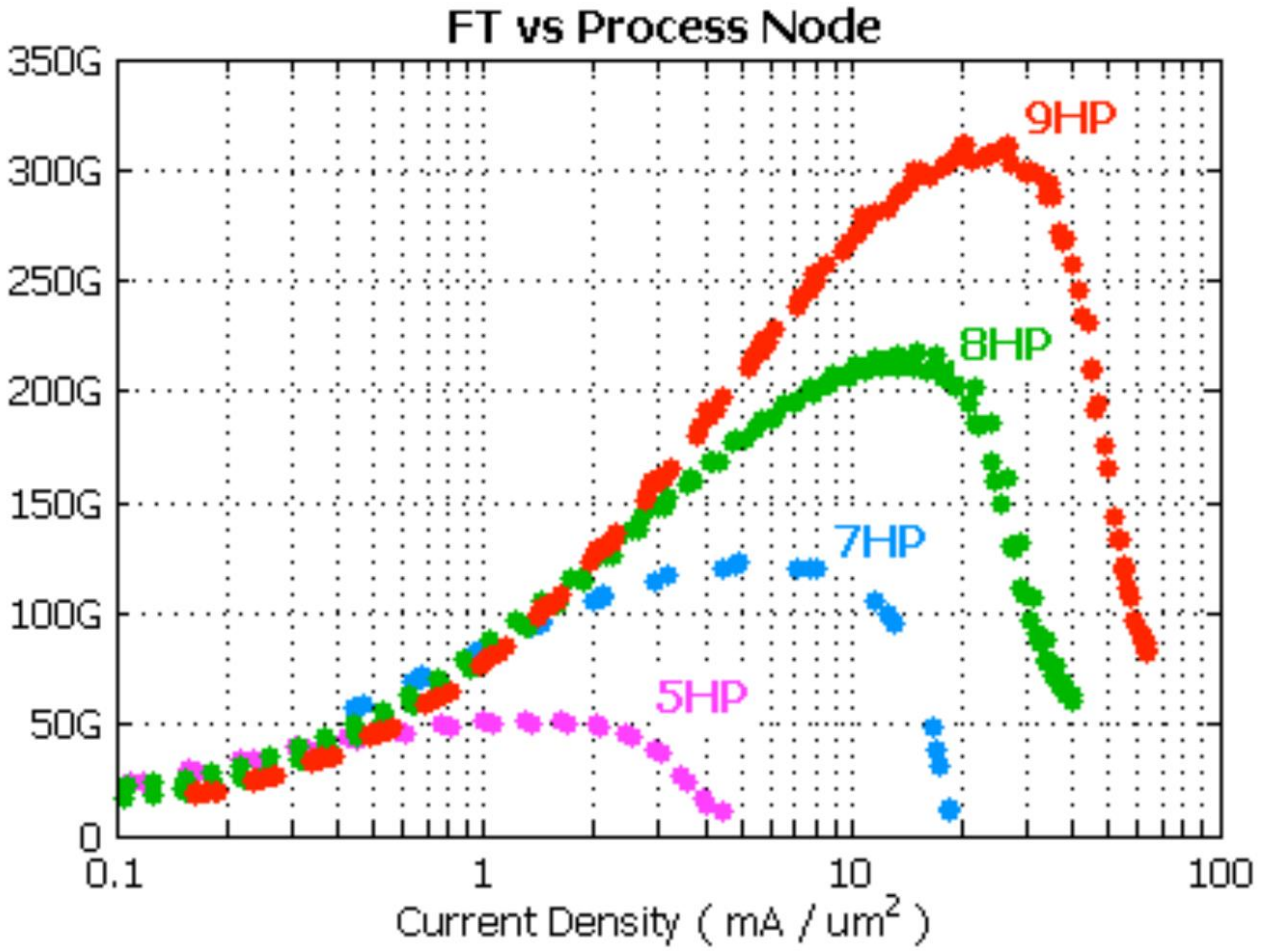
- Nanometer CMOS provides ultra wideband devices (f_{max} & f_T)
- But, we can't build circuits with intrinsic transistors!
- Impact of BEOL parasitics worse in CMOS than SiGe! (2-3 Generations)



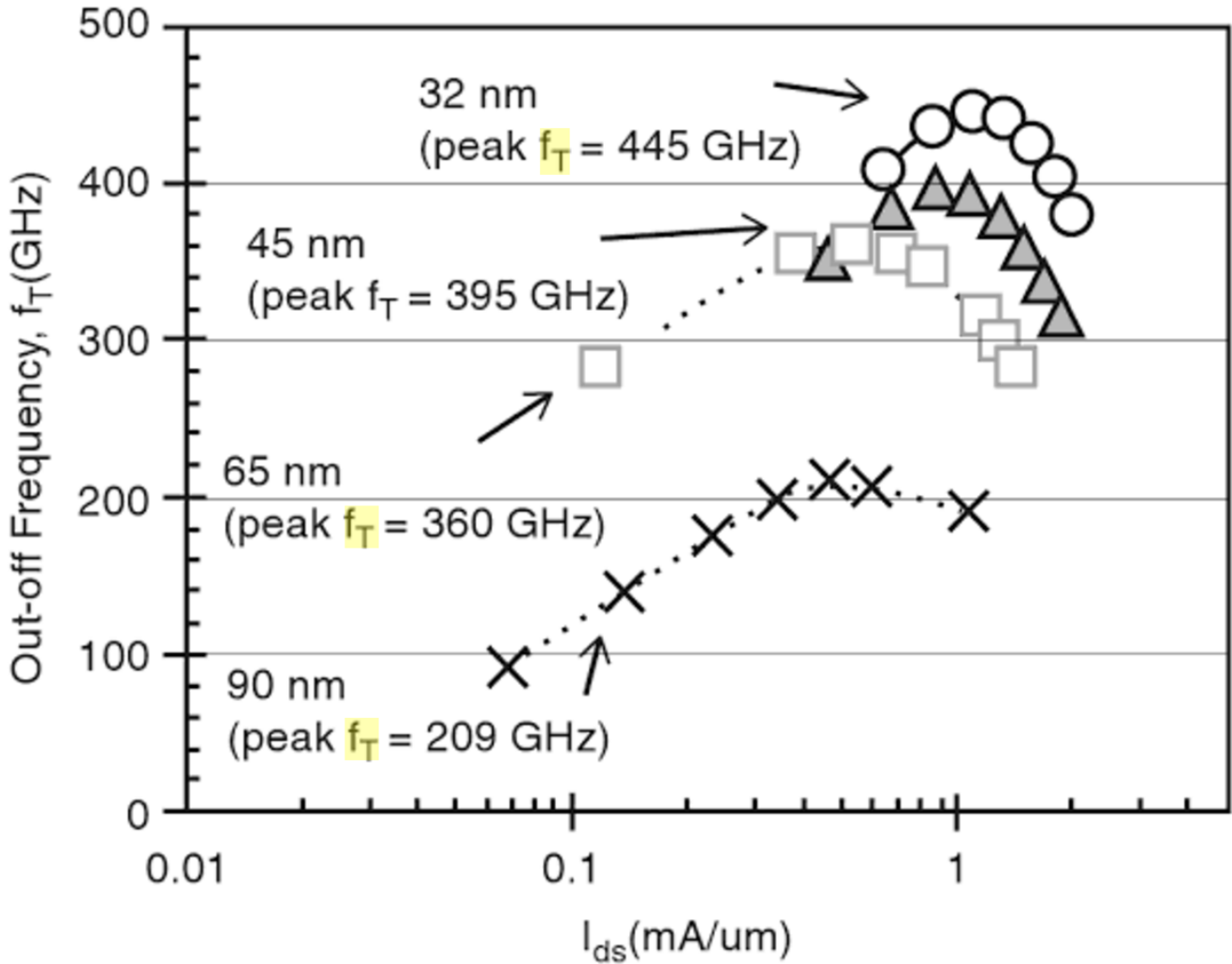
130 nm SiGe HBT



SiGe (IBM) f_T

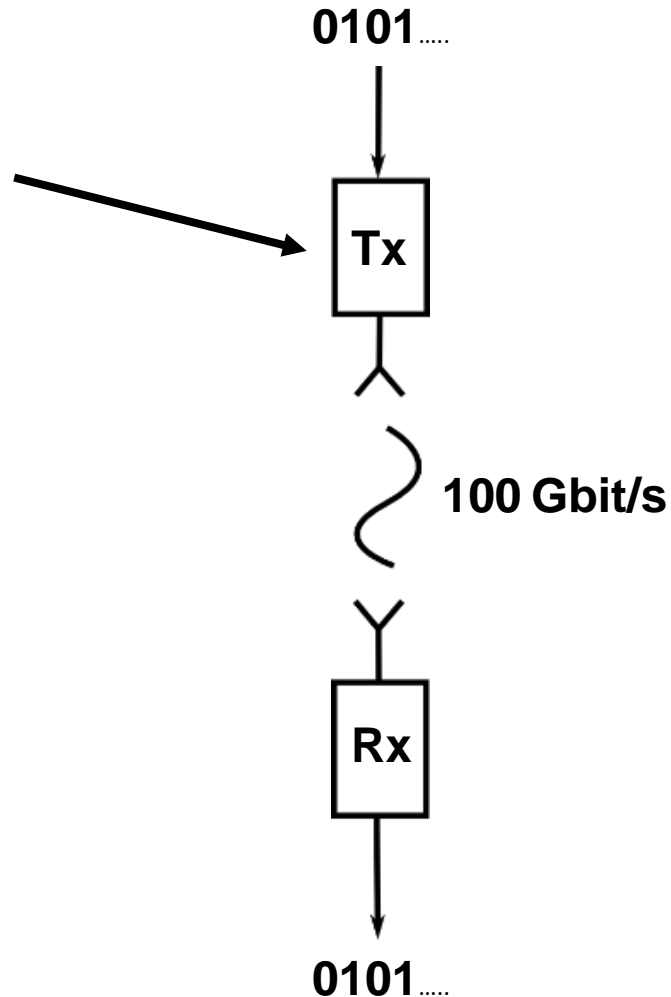


NFET f_T for nm CMOS Processes

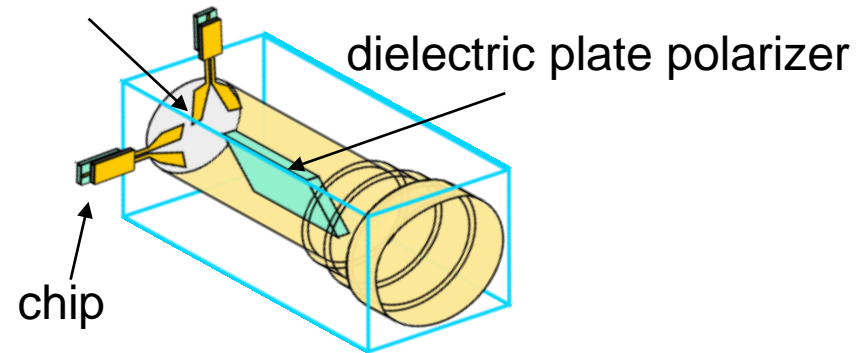
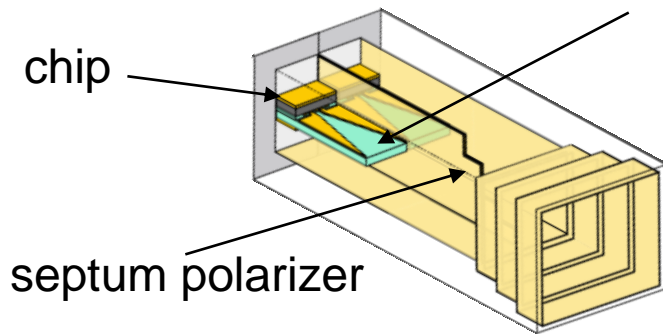
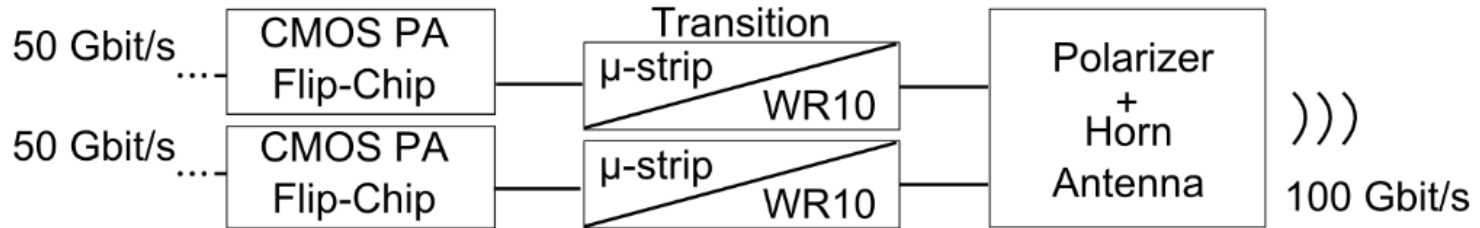


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Overall TX Front-End – An Overview



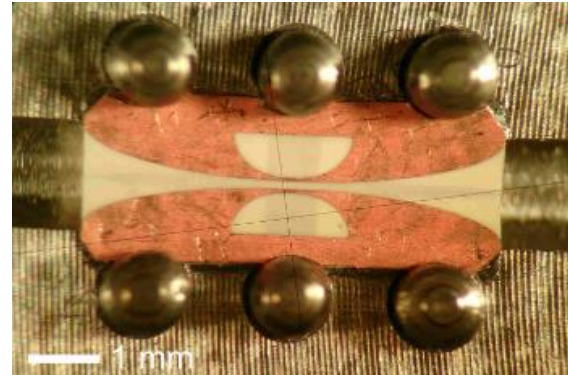
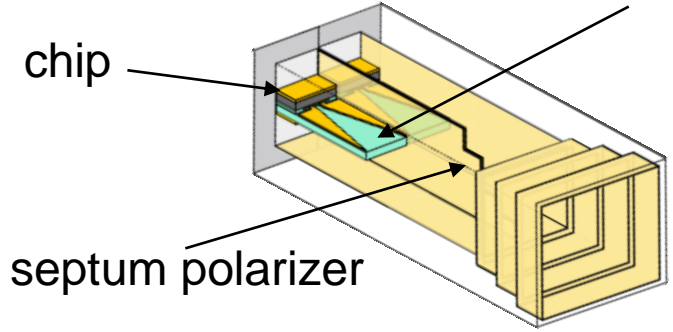
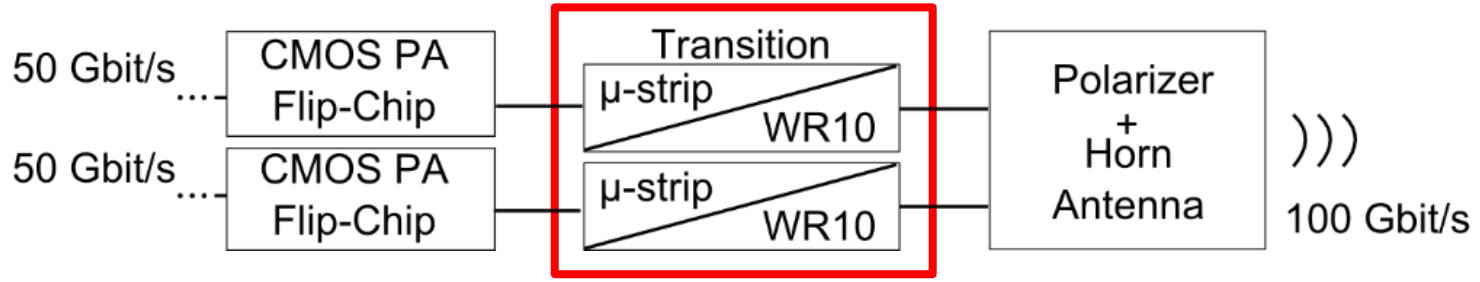
Topology 1

- Inline transition for true brick
- Septum polarizer for compactness

Topology 2

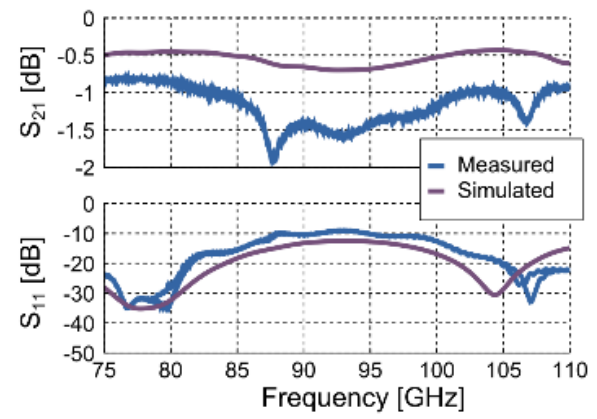
- Vertical transition for dual polarization
- Dielectric plate polarizer for simple setup

Overall TX Front-End - Transition



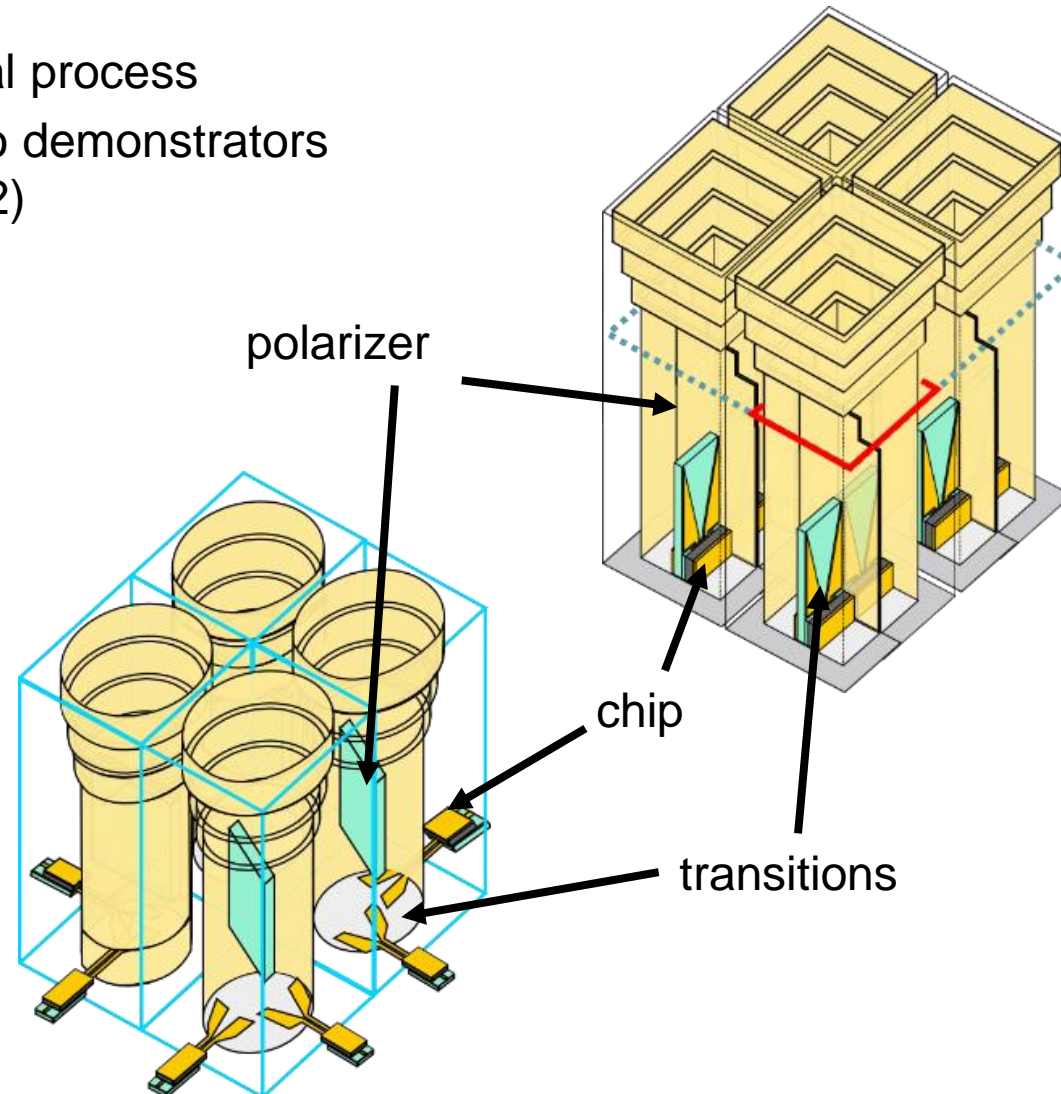
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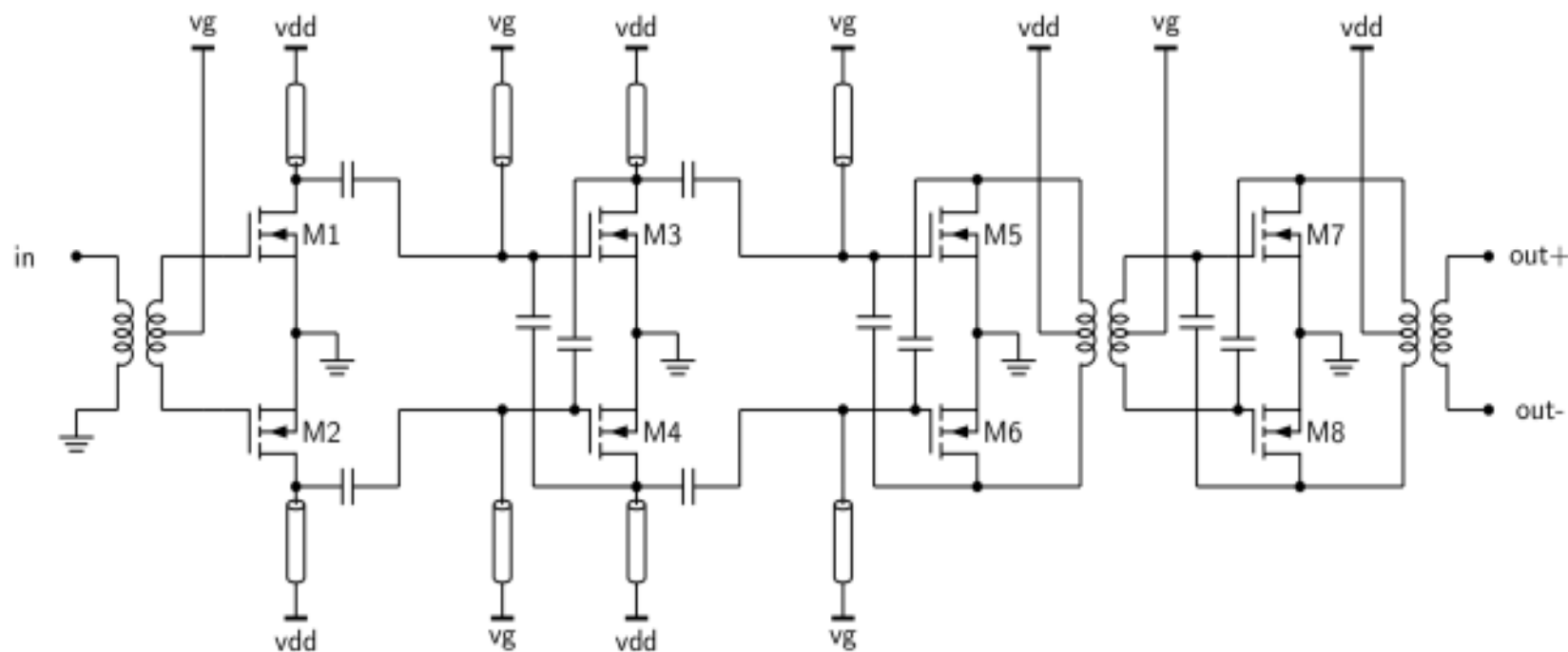
Active Antenna Array for Transmission

- 3D polymer-metal process
- Production of two demonstrators (topology 1 and 2)



W-Band Power Amplifier Design

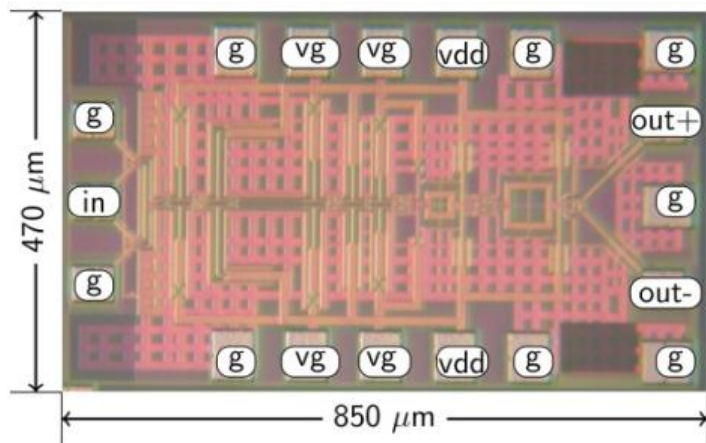
- Challenge → Achieve P_{out} and PAE over 38 % relative bandwidth



- Features
 - 40 nm CMOS technology, fully differential 4-stage design, neutralized transistors, transformer coupling, broadband matching

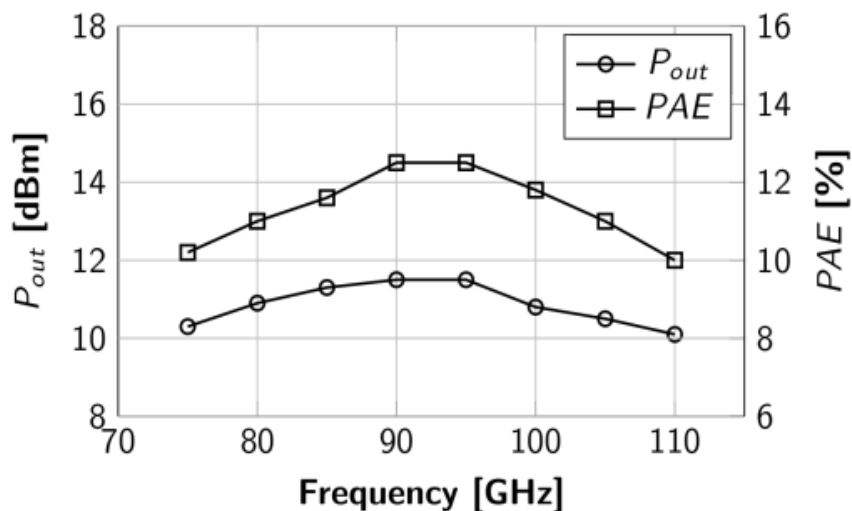
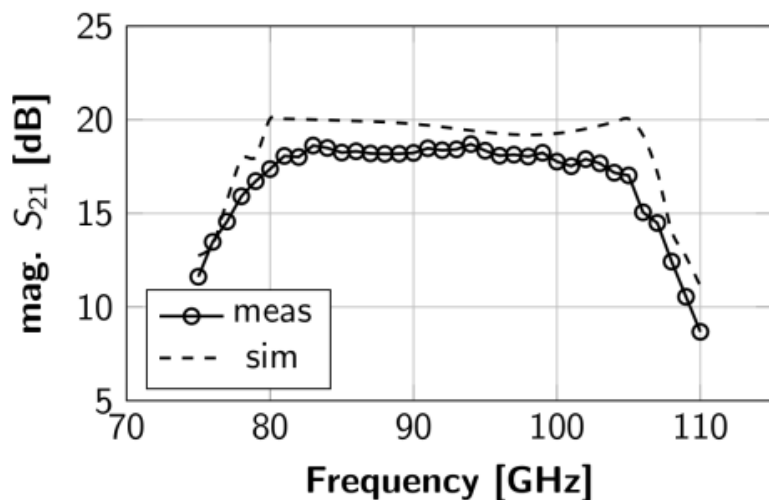


W-Band Power Amplifier Design - Results

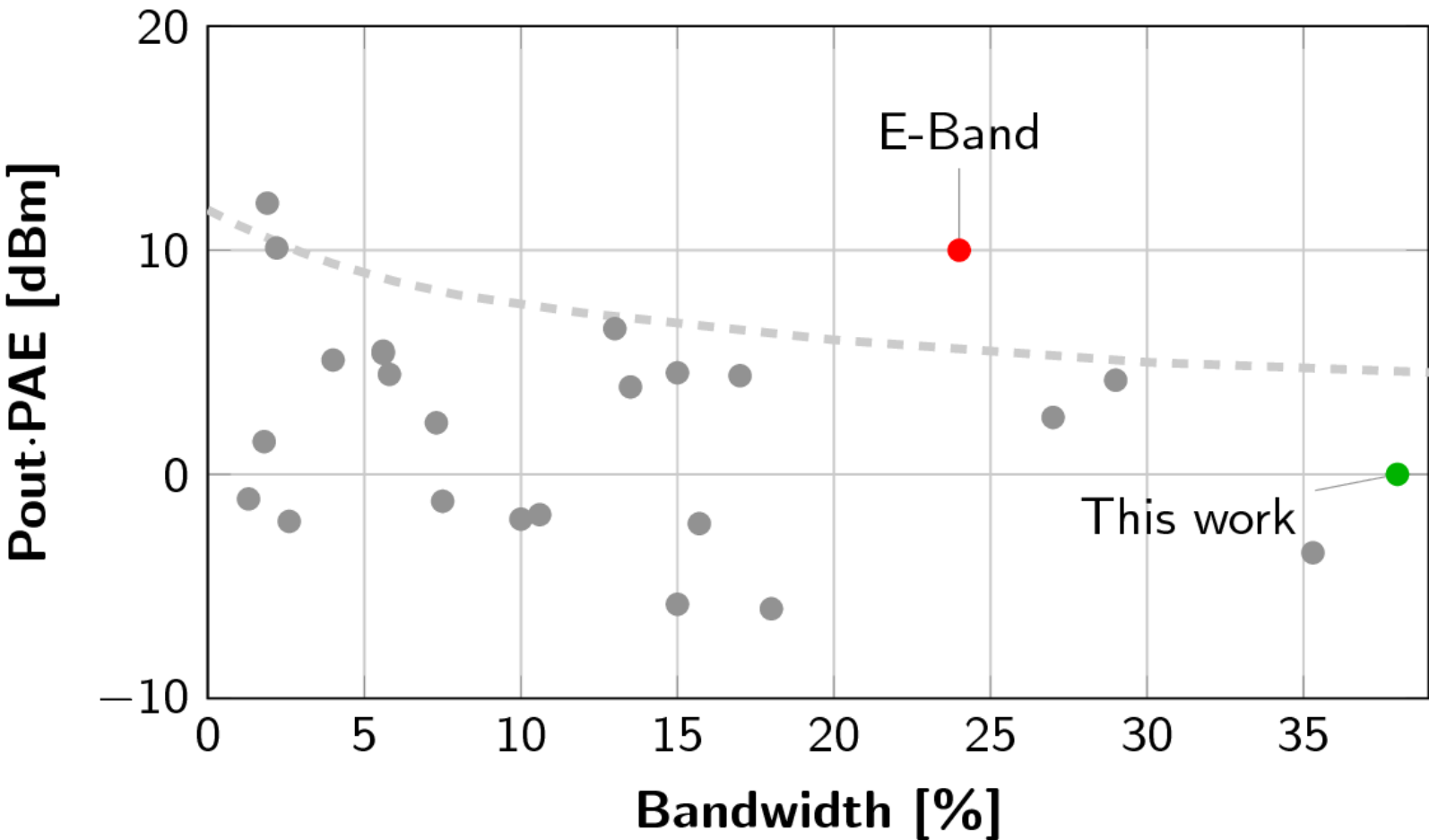


Results

- 18 dB small signal gain
- $P_{out} > 10$ dBm
- PAE > 10 %
- 38 % relative bandwidth
- Good correlation sim/meas.

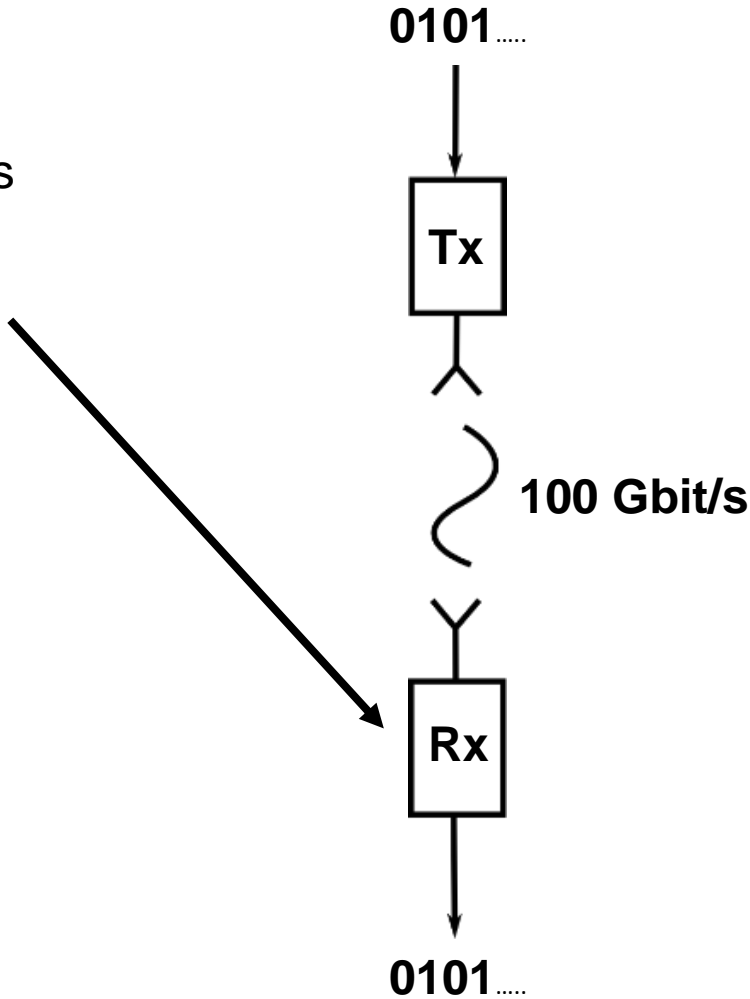


Comparison with state-of-the-art - FOM

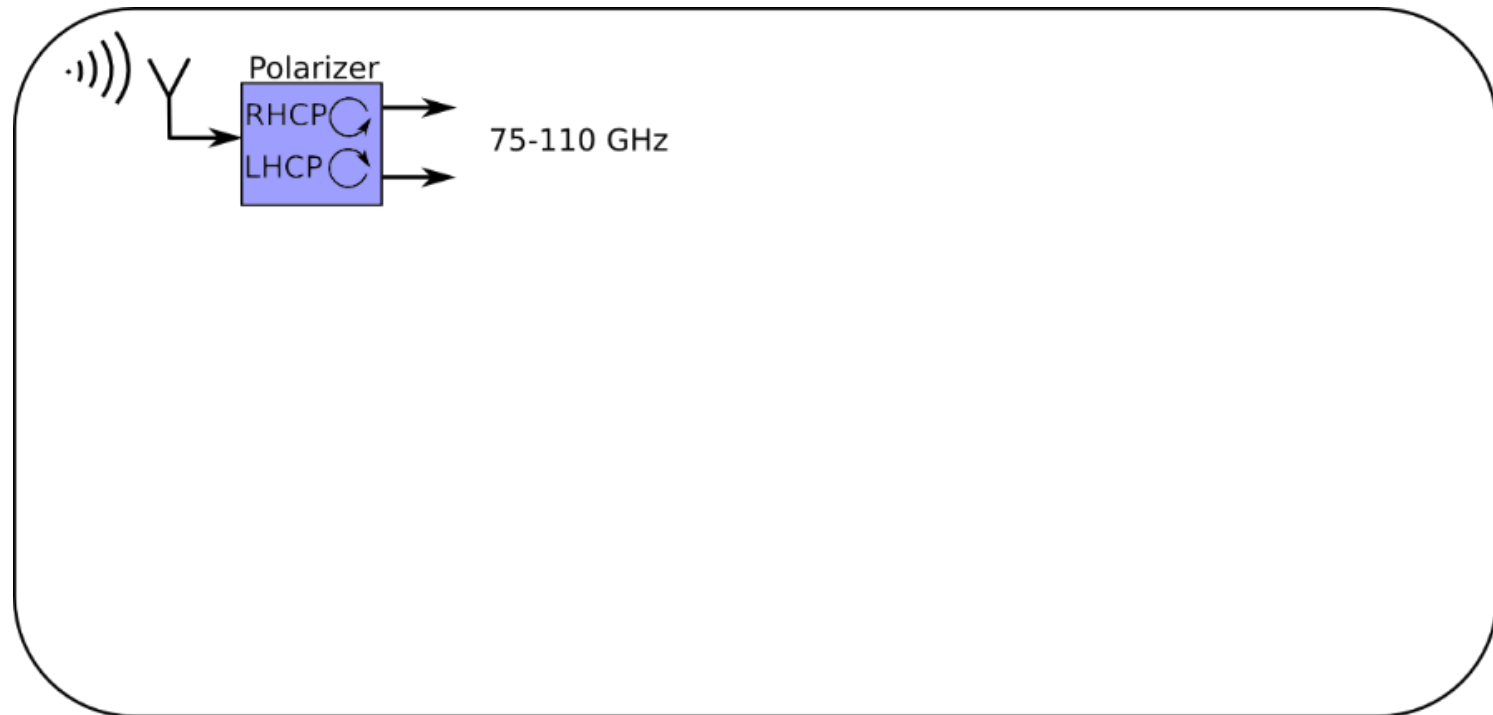


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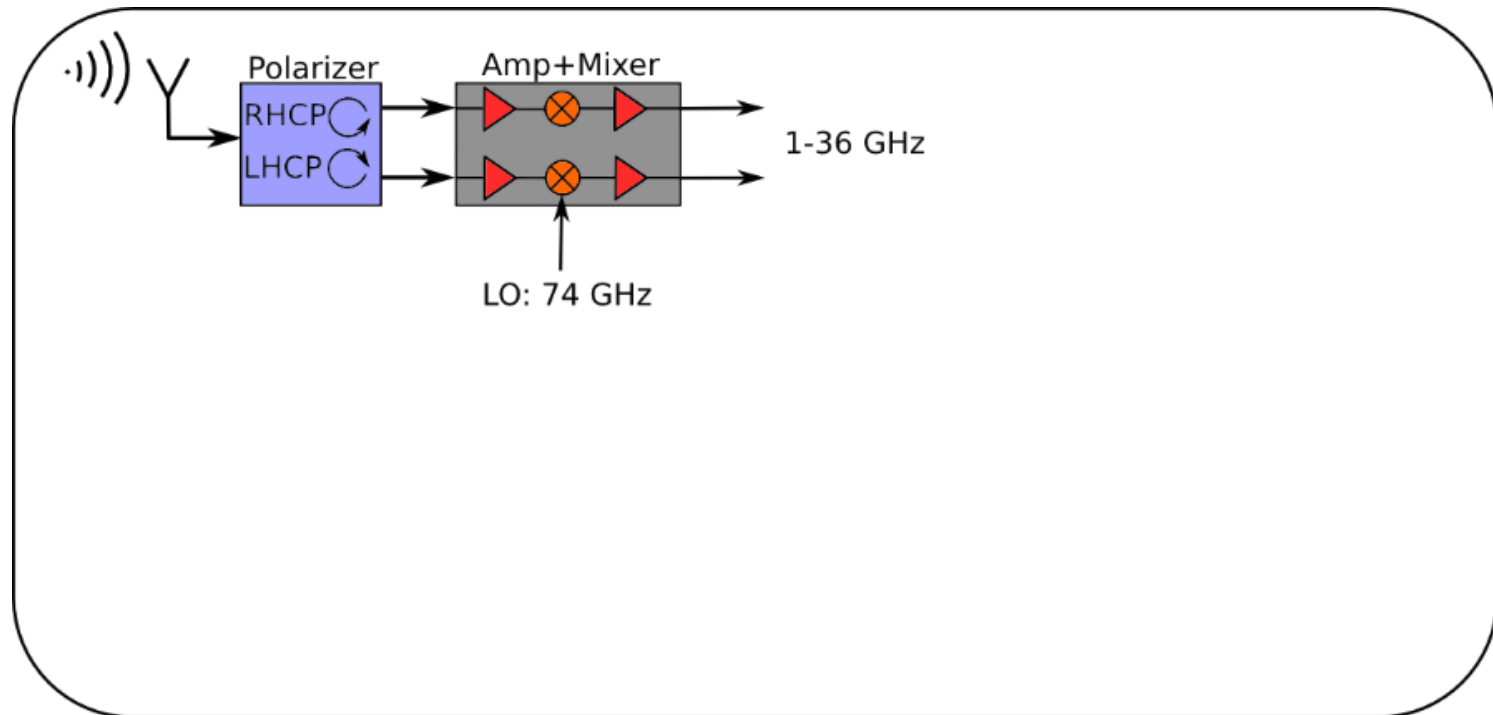


Receiver System



- CMOS chip integration in dual-polarized horn antenna
 - Using 3D polymer-metal process
 - System-in-Package

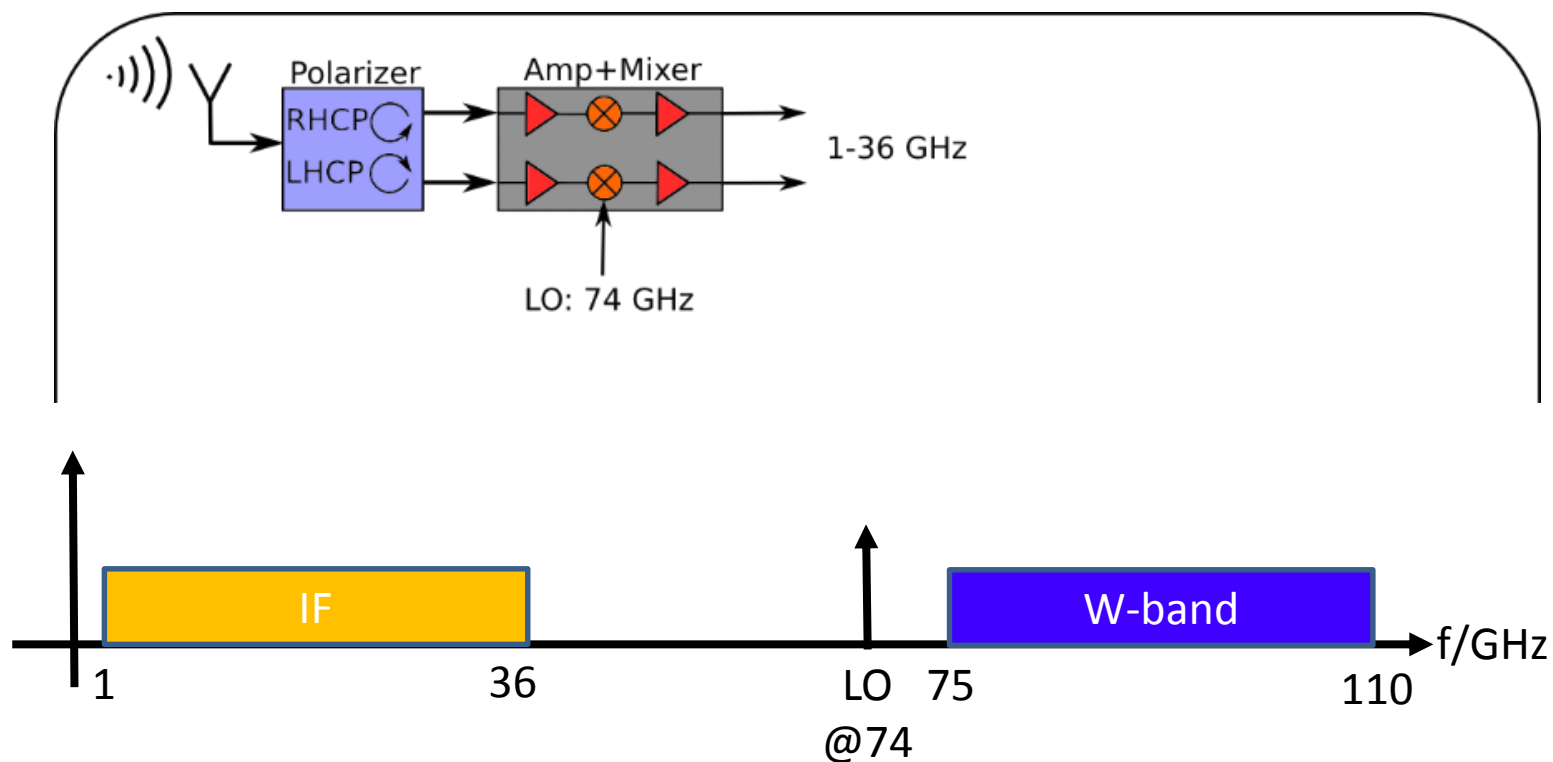
Receiver System



- Single-chip, dual-channel RF-to-digital conversion
- 28 nm high-K metal gate (HPC) CMOS technology
- Full bandwidth low-IF concept (1-36 GHz), no IQ-splitting



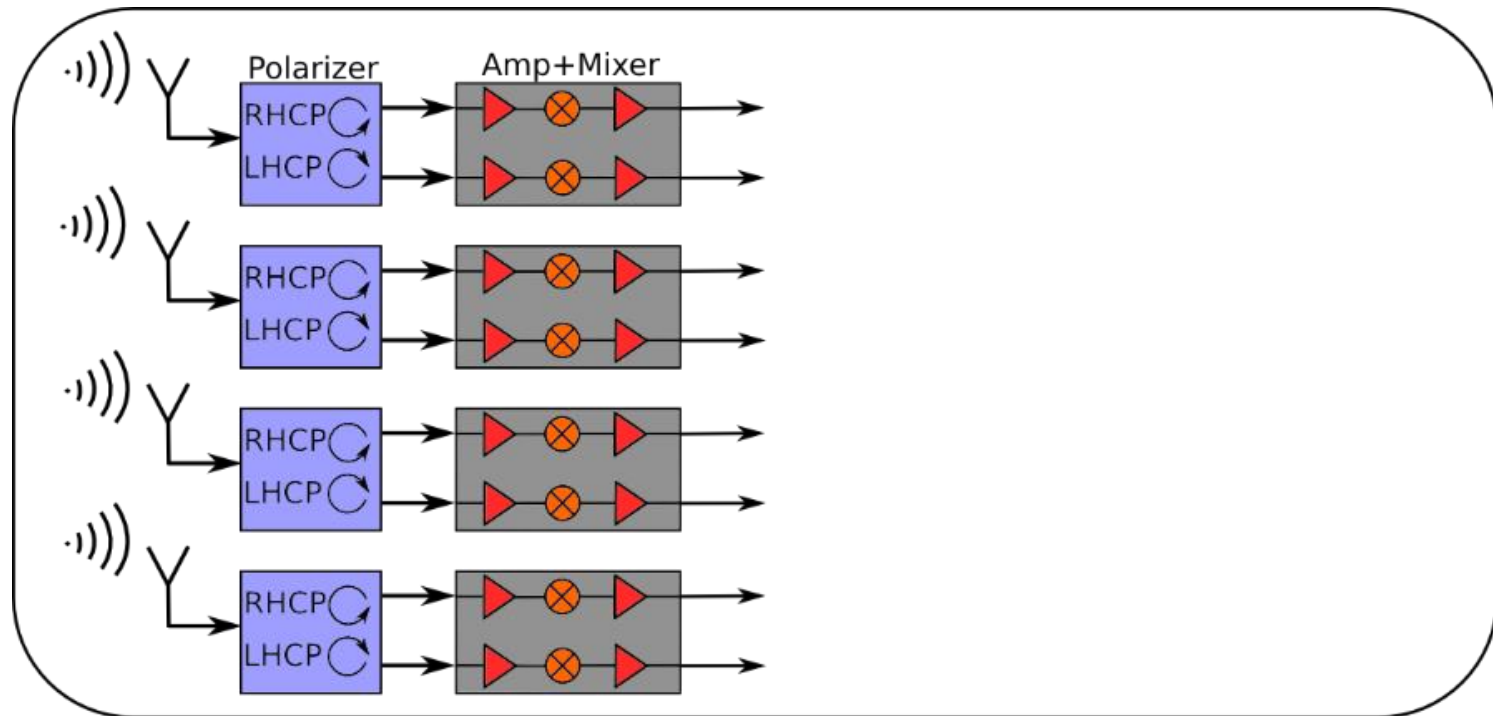
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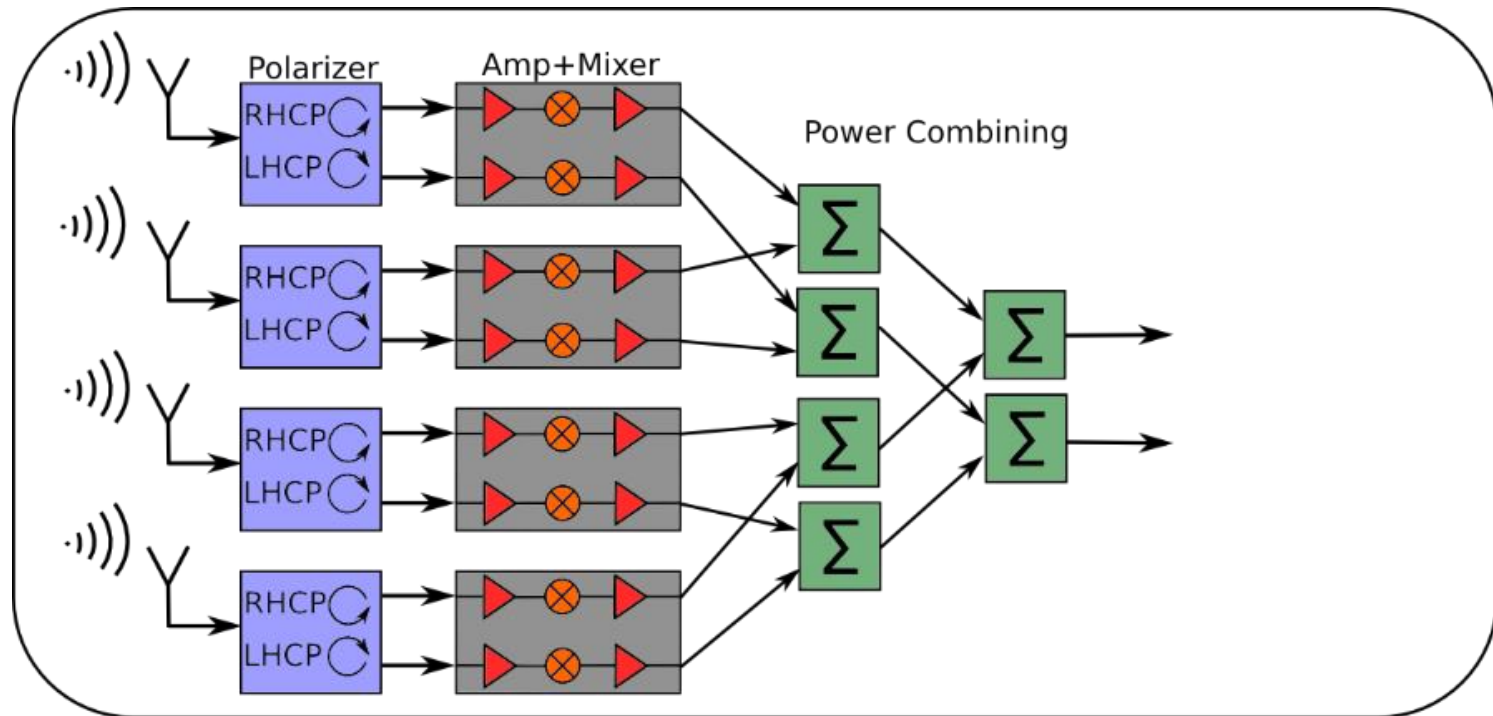
Receiver System



- External LO / clock generation (18 GHz LO to link tests)
 - Two on-chip frequency doubler to 74 GHz
- Beam steering
 - Digital phase shifters

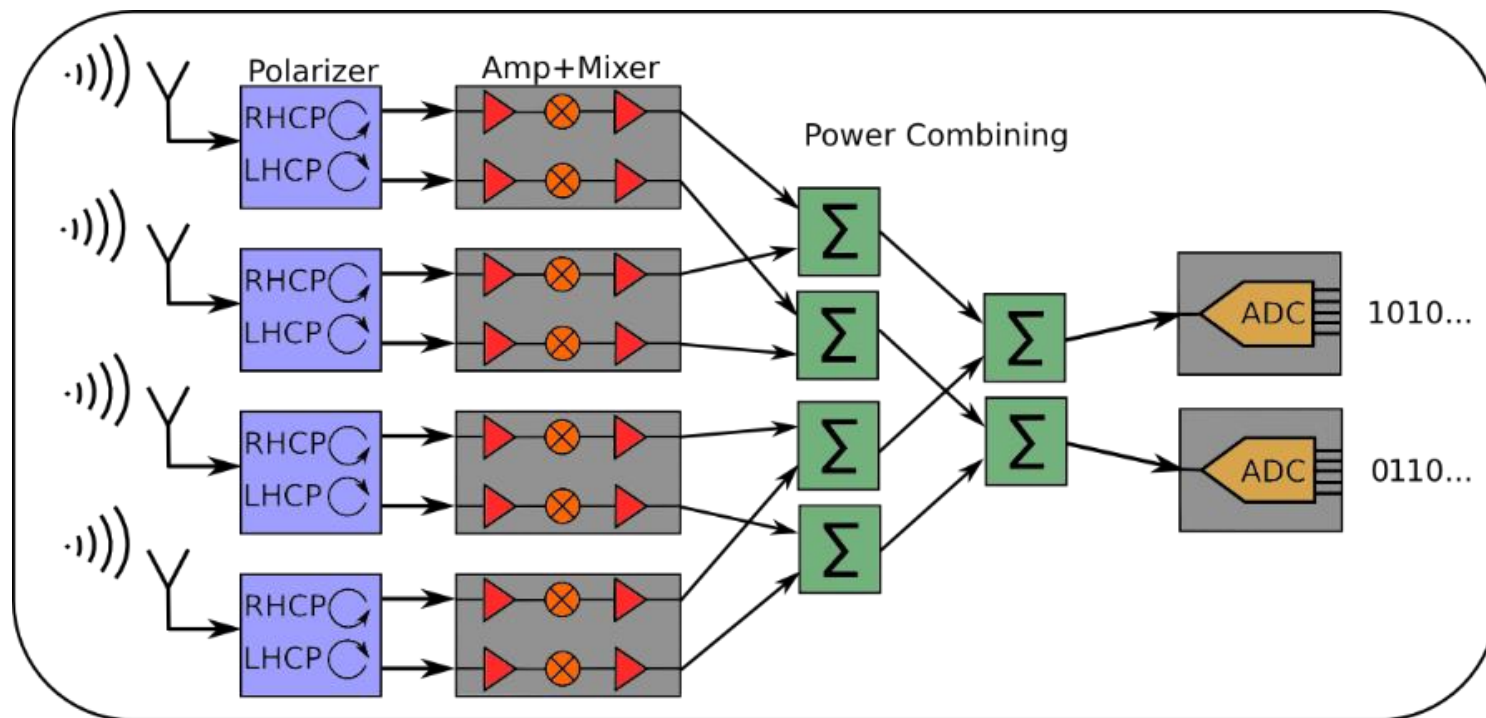


Receiver System



- Power combining at IF
 - Pro: simple
 - Con: channel interference and SNR

Receiver System



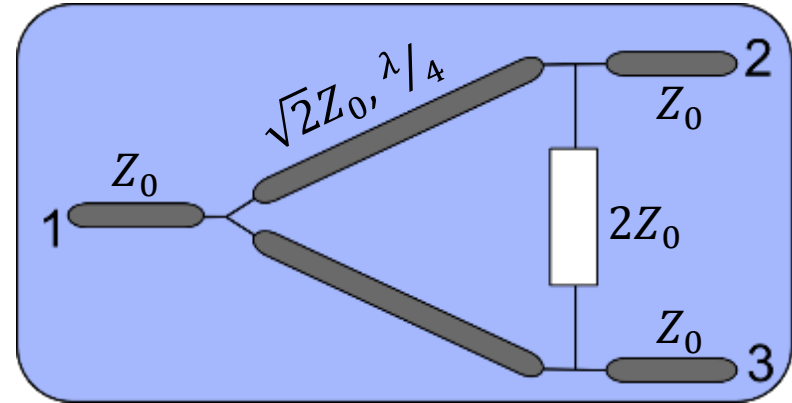
- Impedance-conversion to drive 74 GS/s T&H
- 74 GS/s (time-interleaved) ADC
- 5 bit ENOB
- RF-to-Digital outputs (\rightarrow decimated output or on-chip memory)



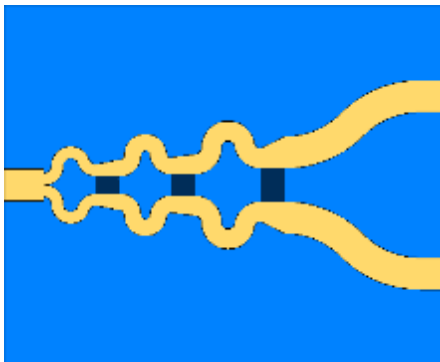
Receiver-Topology - Power Combiner

Wilkinson power combiner

- Limited bandwidth
 - Multiple sections
- Lumped element resistor needed
 - Film-resistors with less parasitics

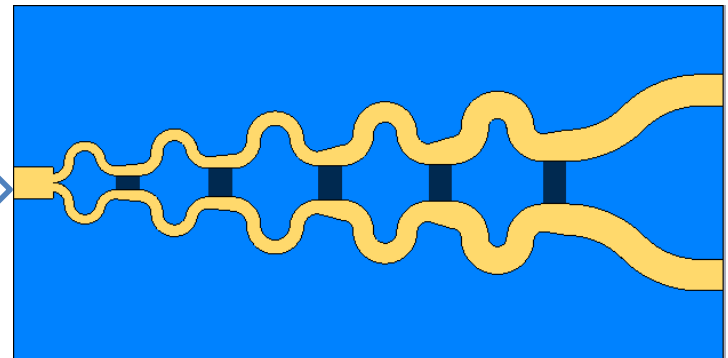


3-Steps

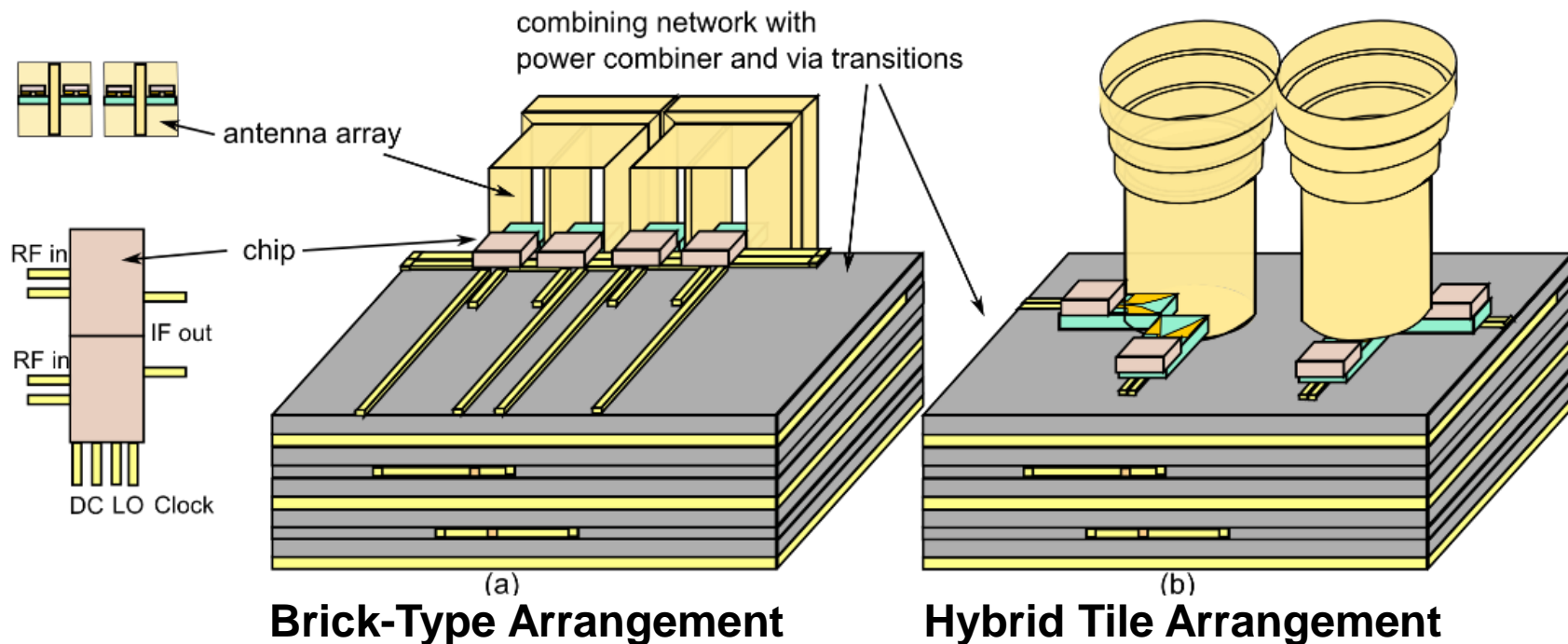


Losses vs. Bandwidth

5-Steps



Receiver-Topology - Antenna Array I

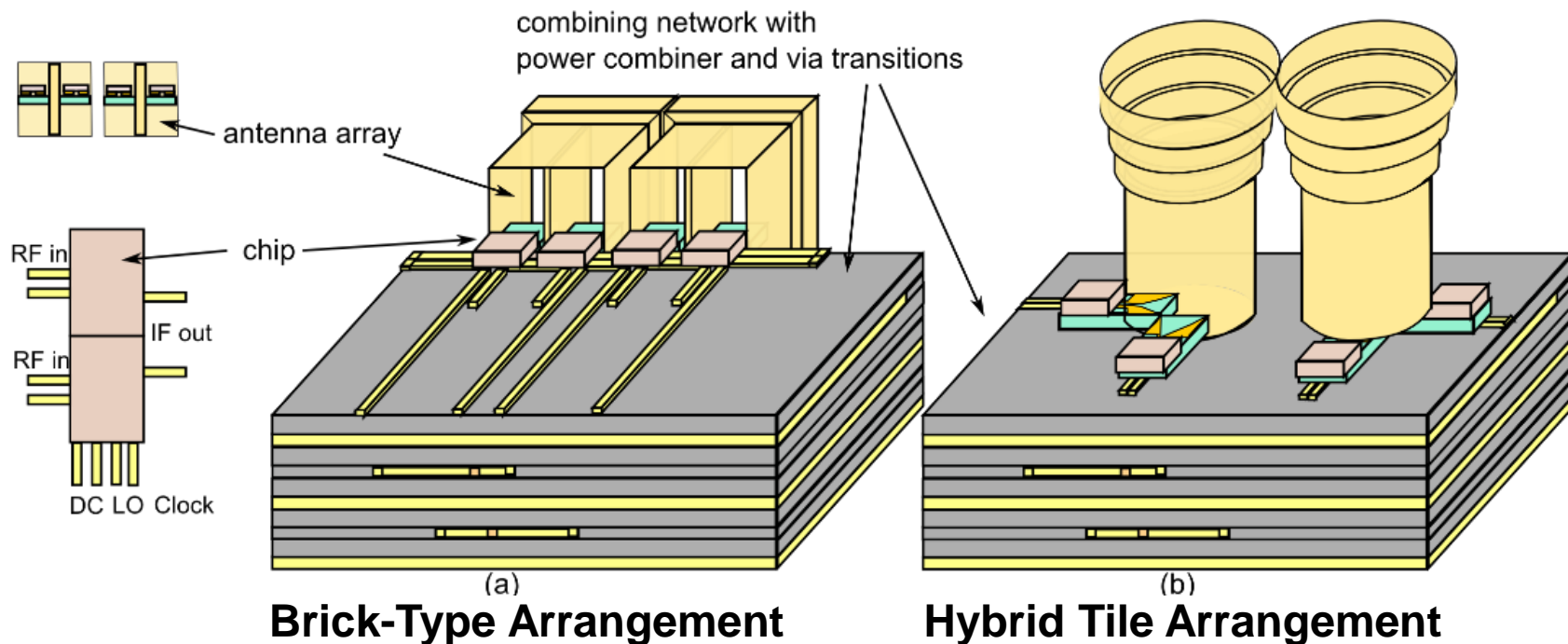


Multi-layer feed network

- Monolithic integration
- 3D polymer-metal process
- LO distribution network and ADC on separate motherboard



Receiver-Topology - Antenna Array II



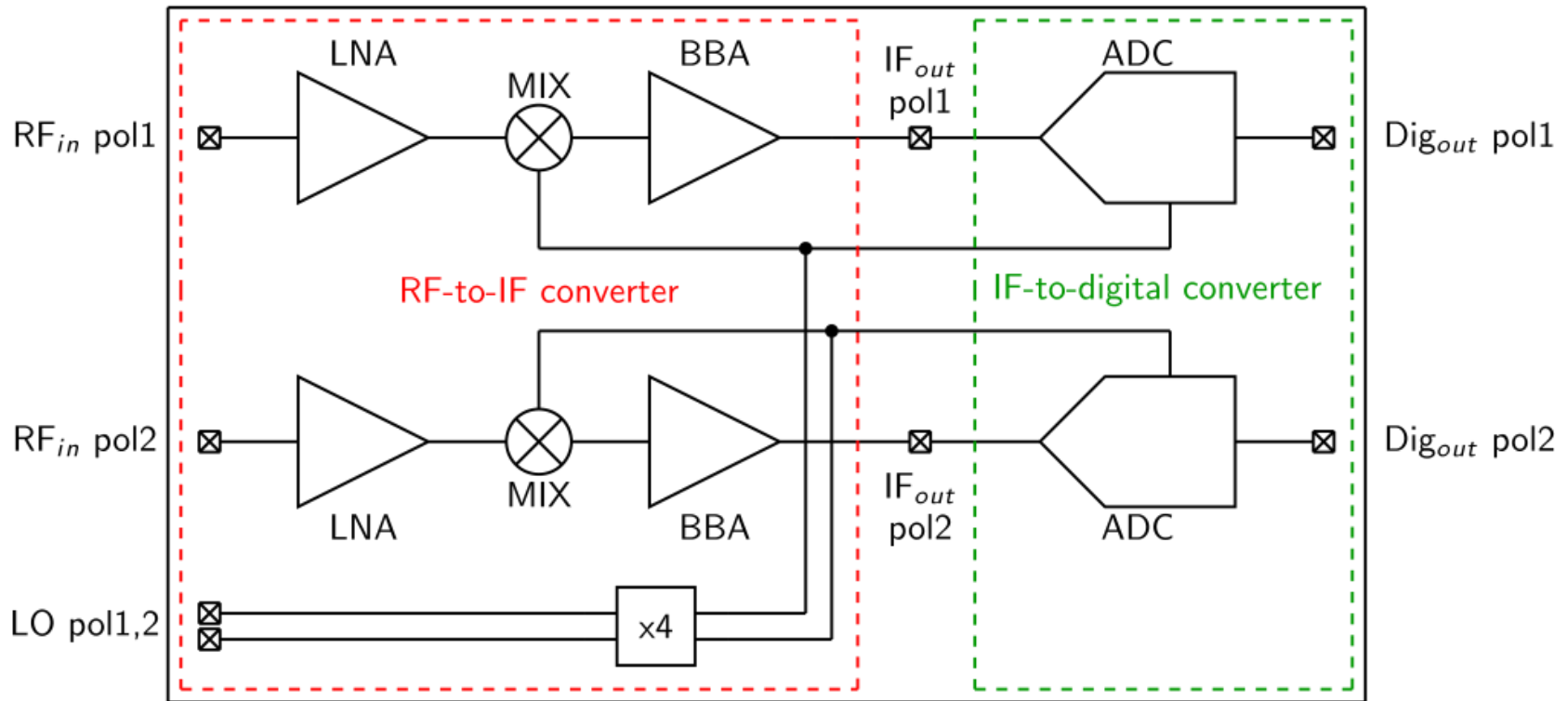
- Feed network in line w/ front-end
- Antenna rows
- Grown layer-wise
- Interconnected on motherboard
- Land- or ball-grid for 2nd level interconnects

- Tile architecture for feed network
- Vertical growth
- Integrated layer interconnect
- Full monolithic 3D integration



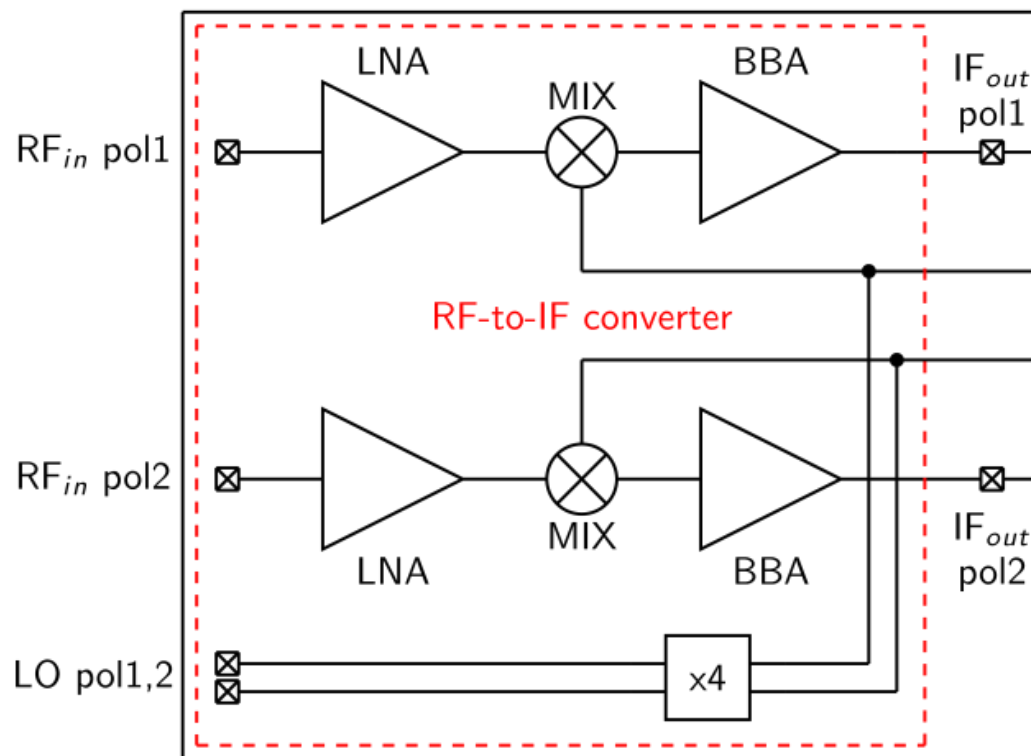
Receiver-Topology - RF-to-IF Converter

- Single-chip dual-channel receiver



Receiver-Topology - RF-to-IF Converter

- Single-chip dual-channel receiver



RF-receiver modules

- 28 nm CMOS
- Low-noise amplifier
- Down-conversion mixer
- Baseband amplifier (BBA)
- LO quadrupler 18 to 74 GHz

Features/Objectives

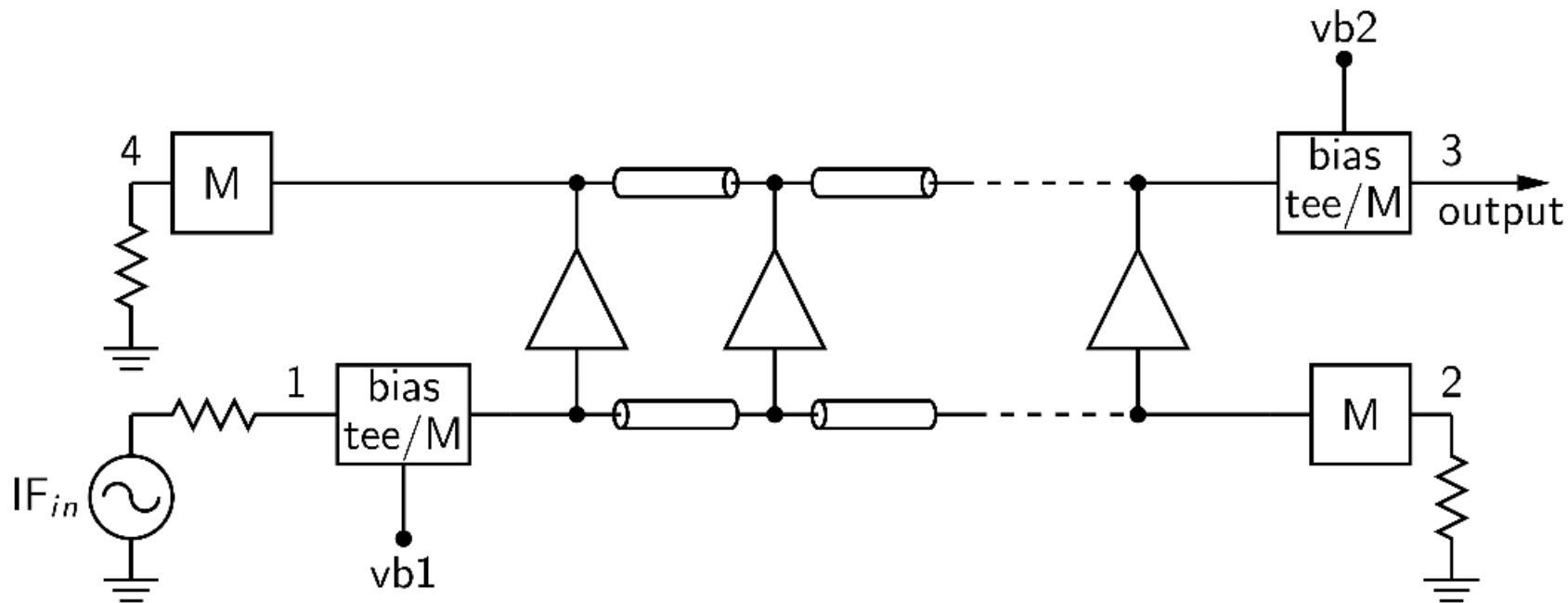
- Full W-band operation
- NF < 7 dB
- Analog gain > 55 dB
- BBA = 1 – 36 GHz (190% BW)
- Output power > 0 dBm

- Design challenge: baseband amplifier with 190 % bandwidth!



Baseband Amplifier 1 – 36 GHz

- How to achieve high gain with 190% relative bandwidth?

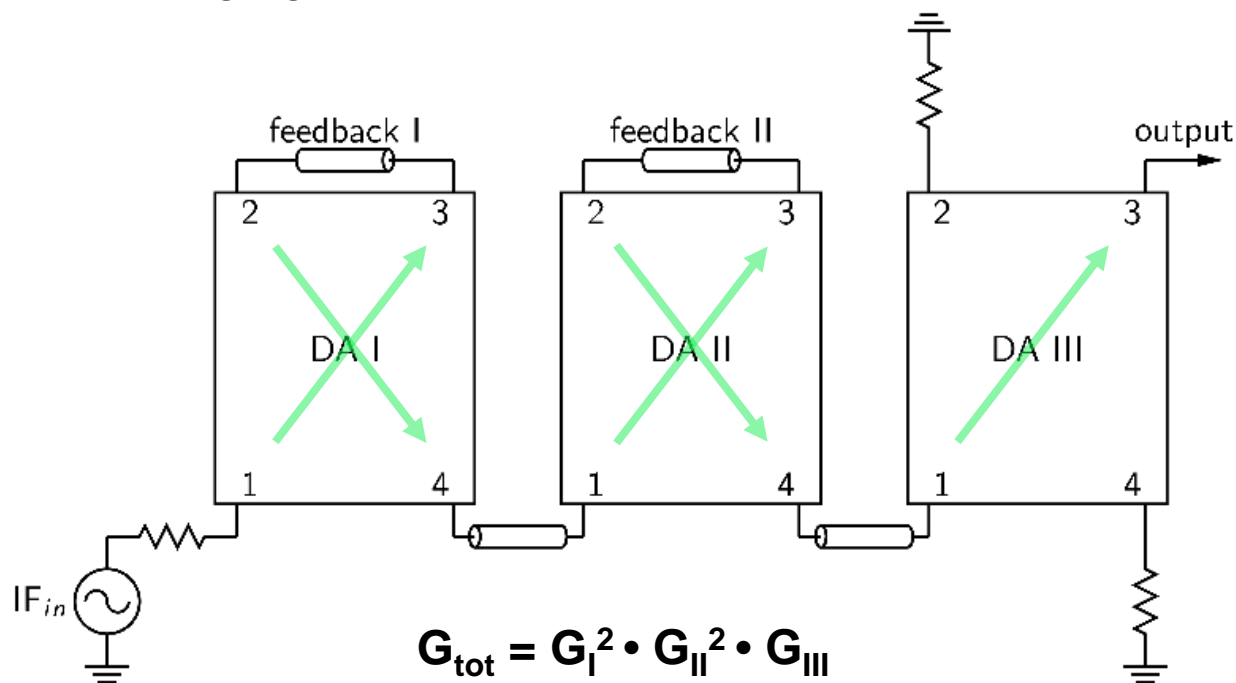


- Classic distributed amplifier (DA)
 - Pro: Inherently broadband
 - Con: low gain



Baseband Amplifier 1 – 36 GHz

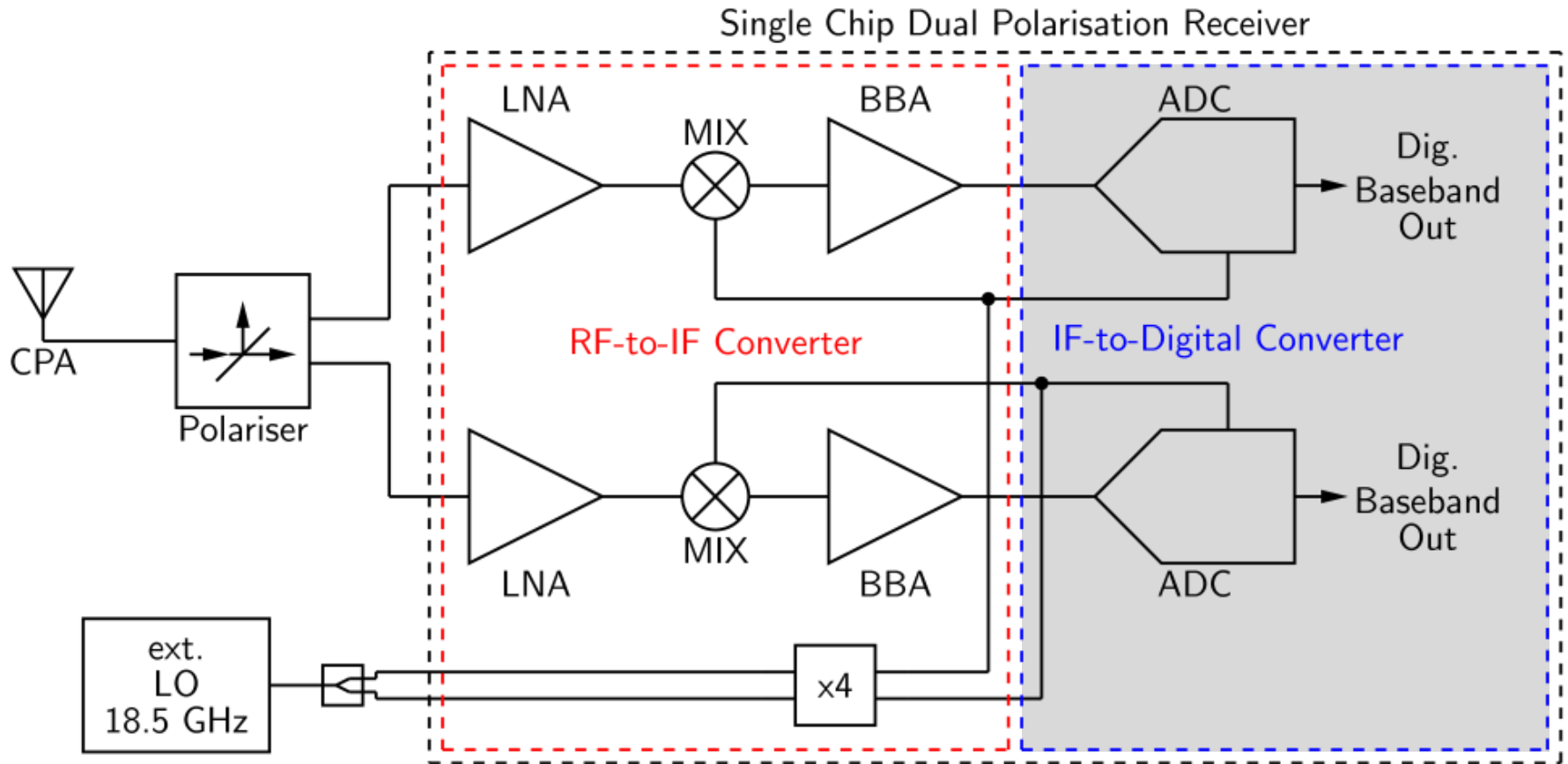
- How to achieve high gain with 190% relative bandwidth?



- Solution
 - Re-use forward and backward gain of DA
 - Multi-stage: combining 3 DA stages $\rightarrow \sim G^5$



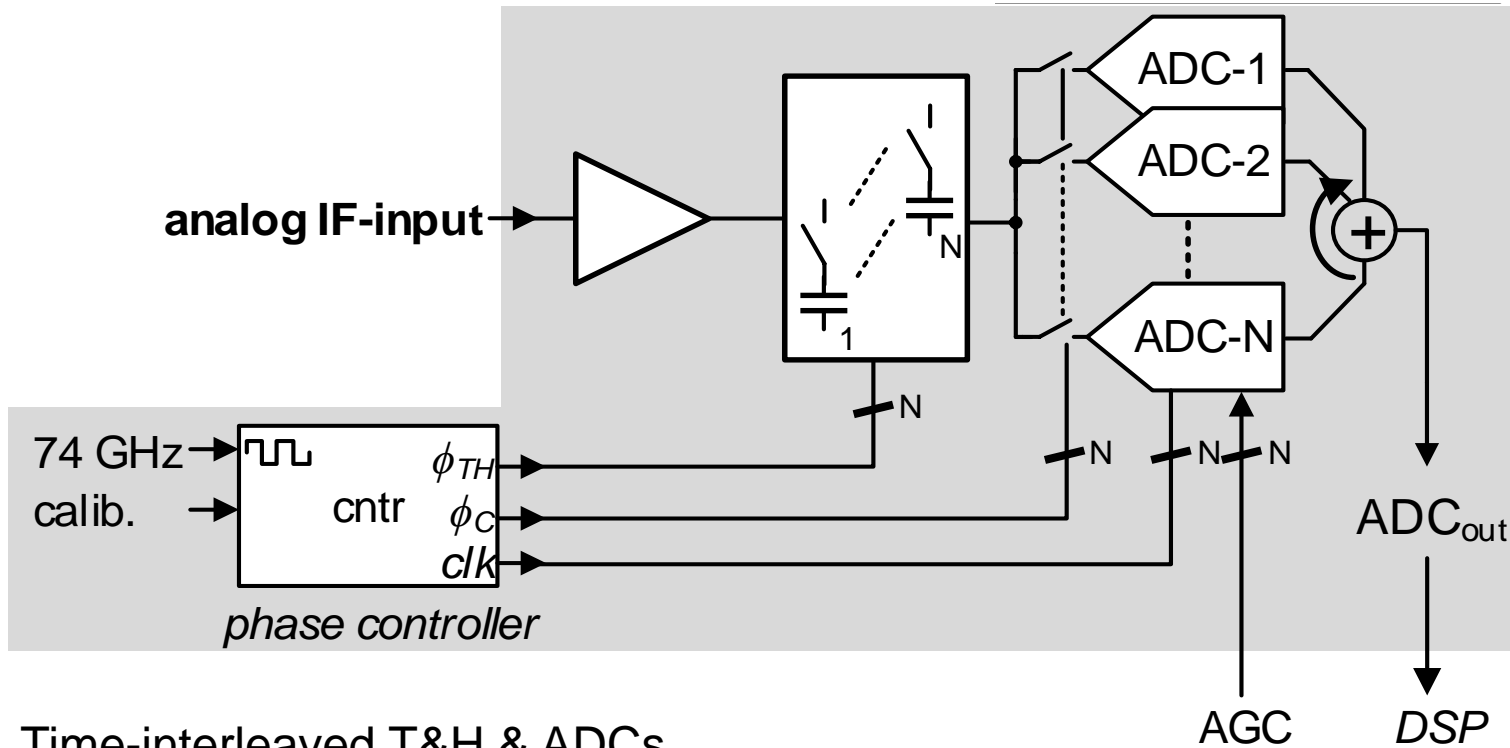
UWB IF-to-Digital Conversion – Overview



- Ultra-wideband (74GS/s) digitizer (direct UWB IF-to-digital conversion)
- >350Gbit/s effective RX resolution enabling simple modulation schemes (BPSK, QPSK) as well as channel equalization (offline)



UWB IF-to-Digital Conversion – Overview

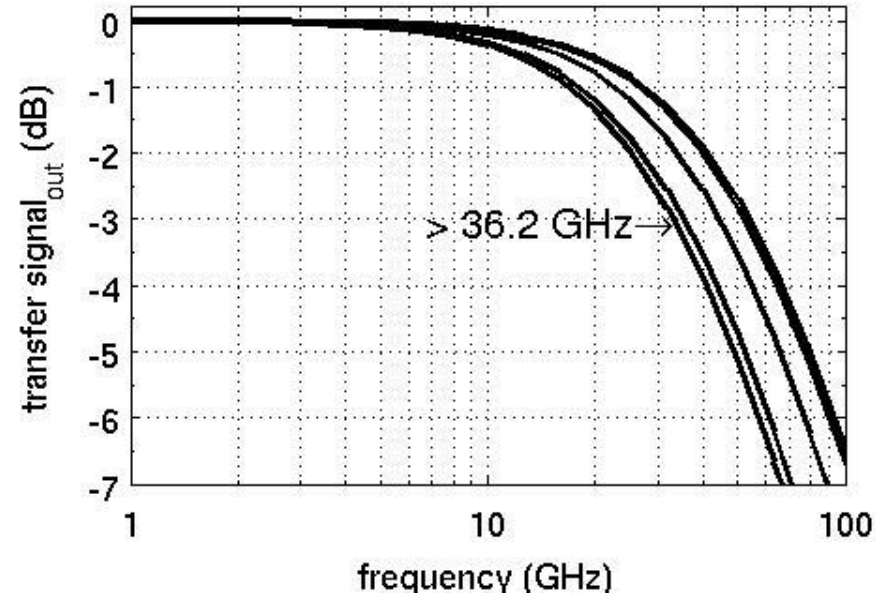
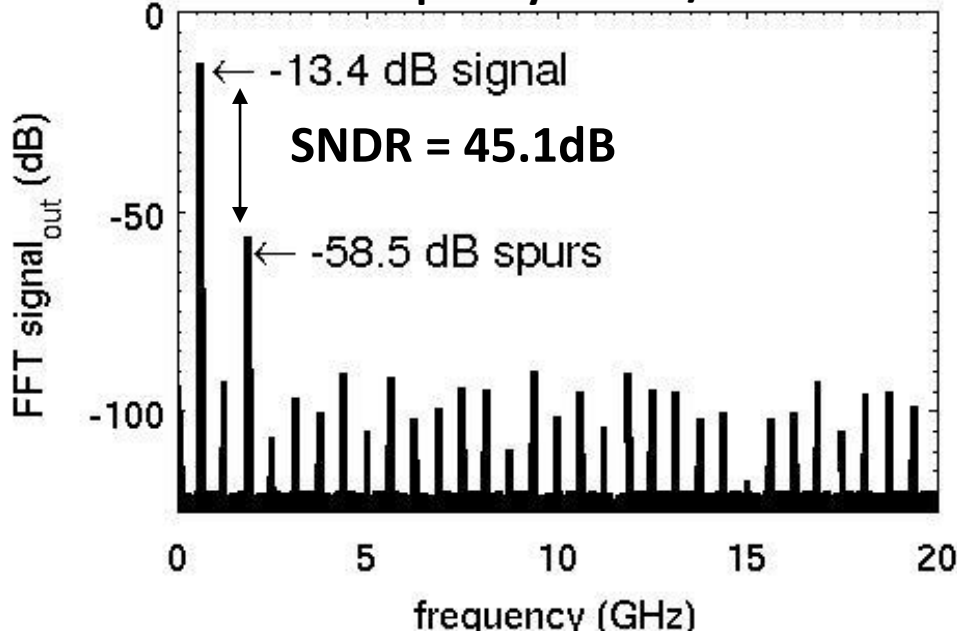


- Time-interleaved T&H & ADCs
- Impedance-conversion to drive T&H
- 40GHz T&H bandwidth with 6bit ENOB



CMOS 28nm Technology Test

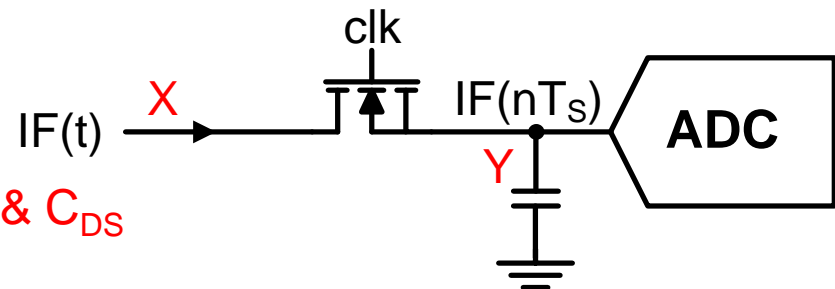
IF over frequency and SS/FF corners



- $R_{on} = 10-40 \Omega$
- $f_{T,n}(TT) = 120 \text{ GHz}$
- $C_{min} (kT/C) = 50 \text{ fF}$

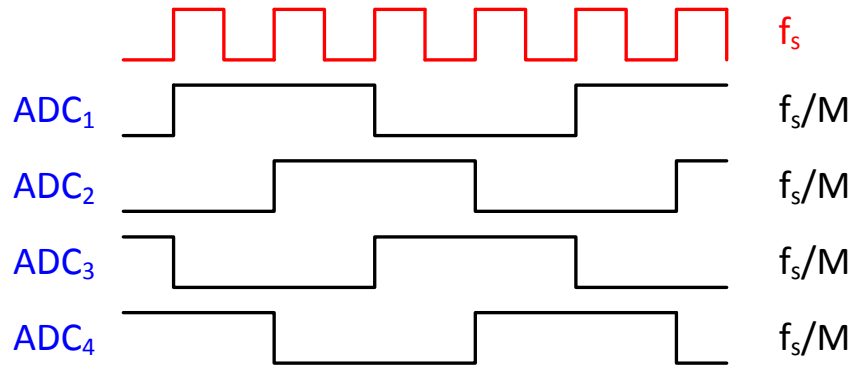
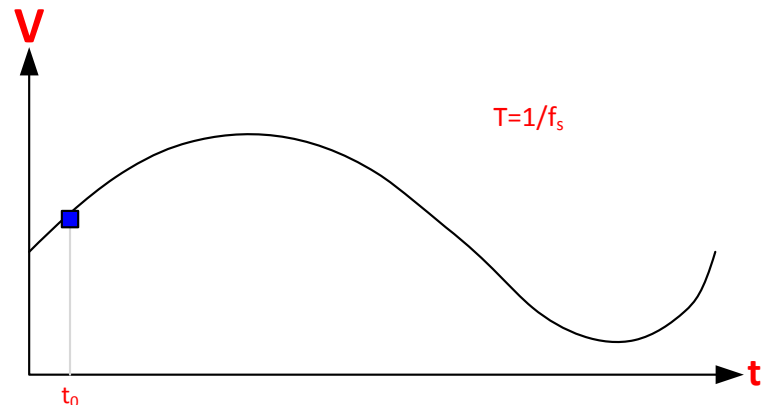
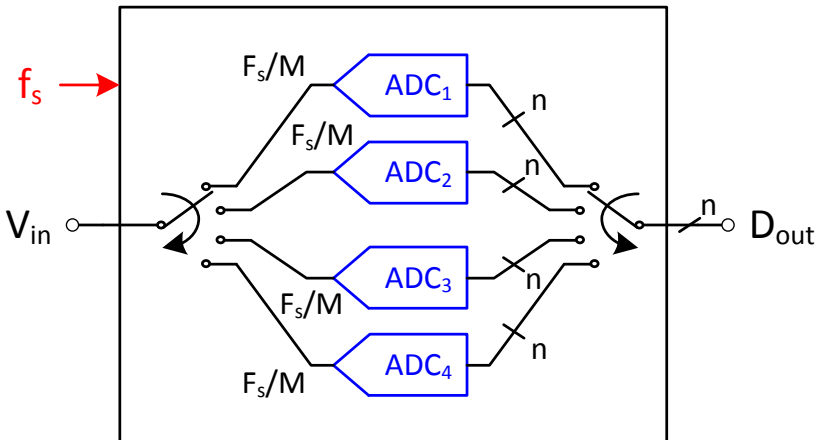
▪ **Challenge:**
switch performance limitation due to C_{GS} & C_{DS}

SNDR = 45.1 dB → 7.2 bit ENOB



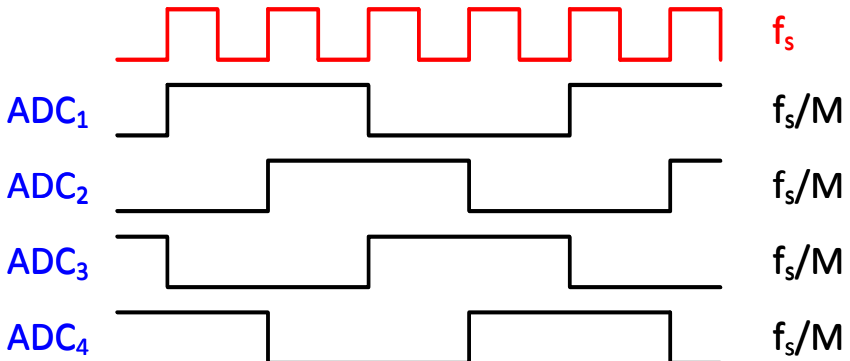
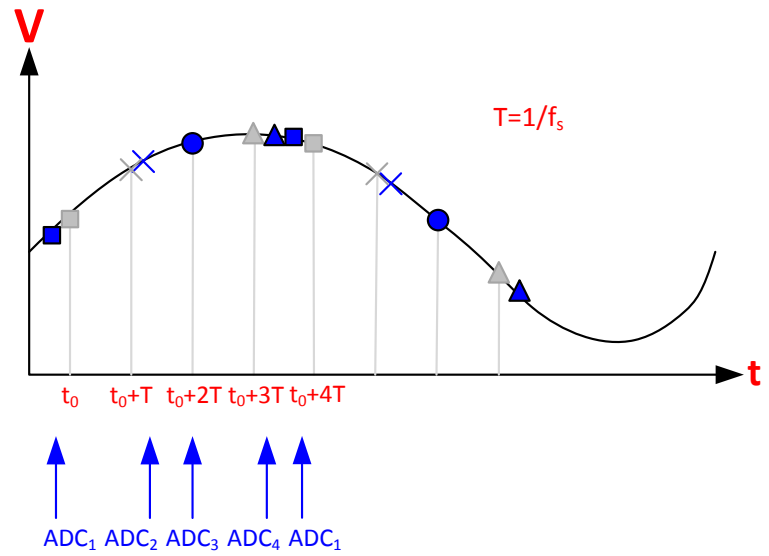
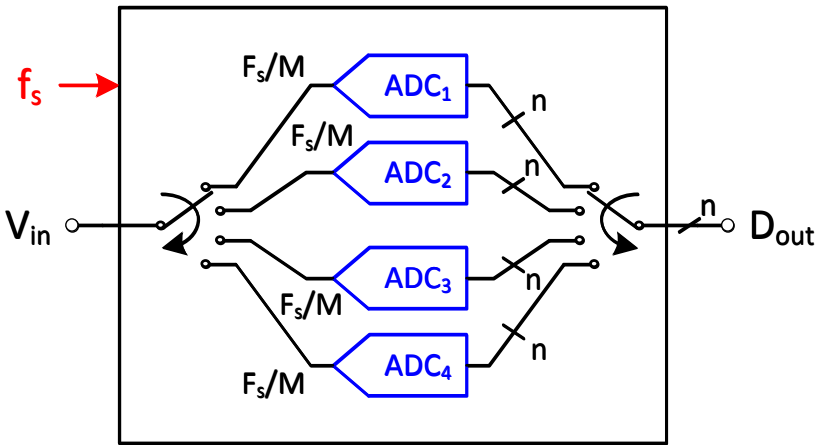
Time-Interleaved ADC

- Time-Interleaved ADC uses many parallel ADC channels operating at a lower speed (comparable with multiple CPU cores)



Time-Interleaved ADC

- Time-Interleaved ADC uses many parallel ADC channels operating at a lower speed (comparable with multiple CPU cores)



- Digital gain and offset mismatch calibration
- Mixed-signal timing mismatch calibration

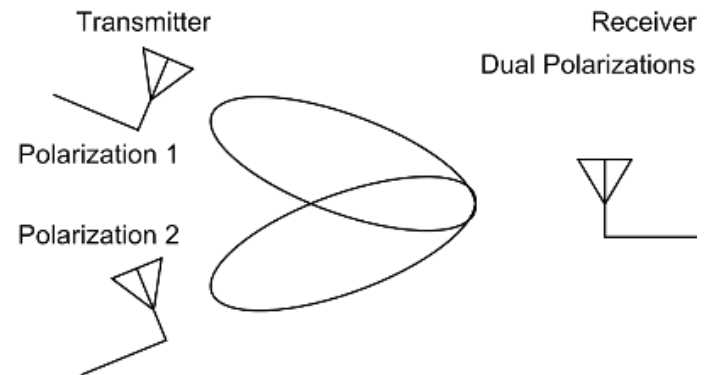


100 Gb/s System Demonstrator

- CW system performance (TUHH anechoic chamber)
- Digital data communication
 - (Univ. Duisburg-Essen, SPP 1655/2 - Tera50+, Prof. Stöhr)

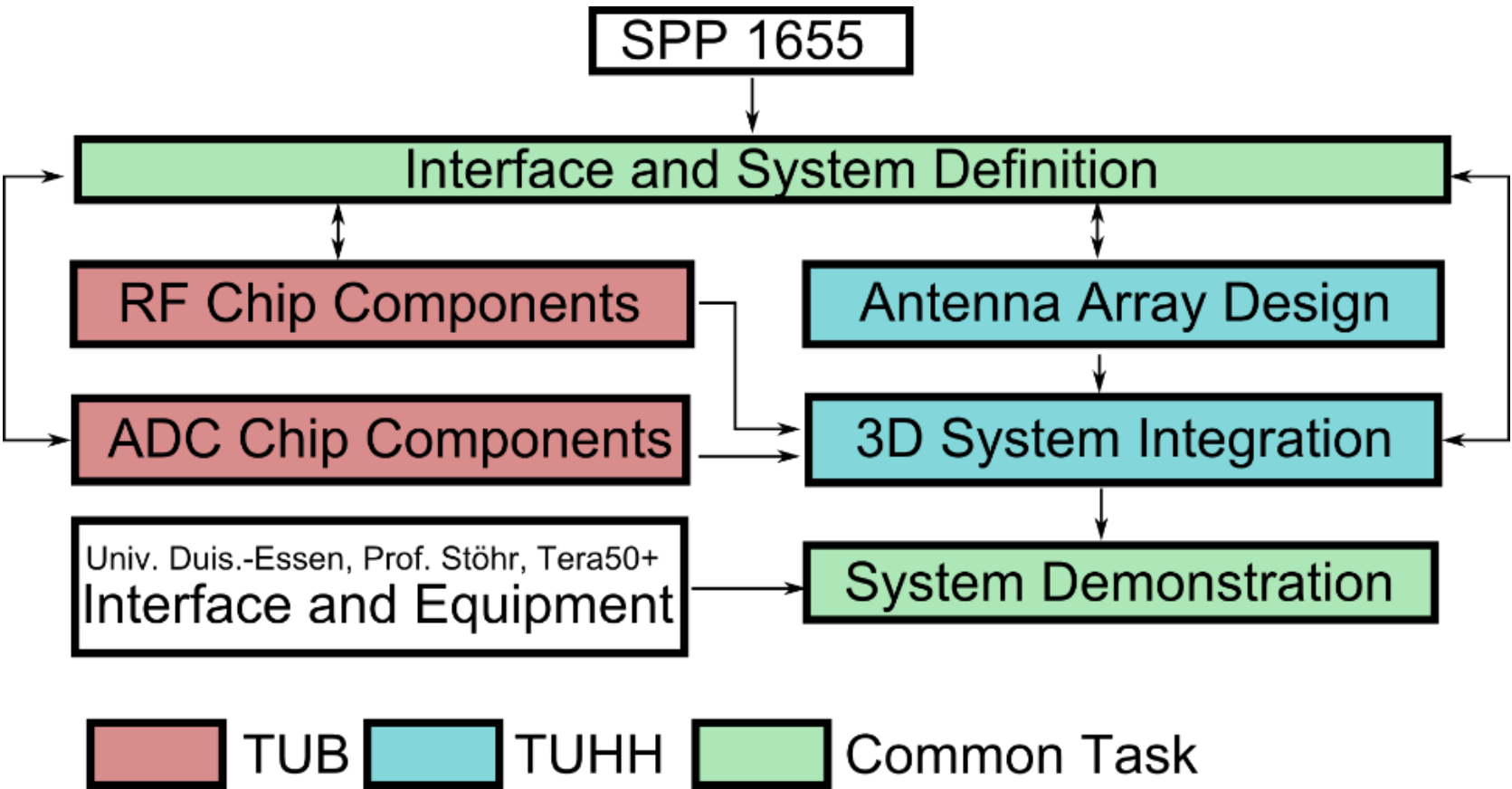
2 Options

- Analog IF outputs
- Digital outputs



System-level demonstration of 100 Gb/s W-band communication with digital beam steering

Collaboration Concept



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Conclusions and Outlook

- **First project phase:** fully integrated low-cost transmitter with
 - CMOS BBPA and antenna array
 - dual circular polarization
 - system integration: work in progress

- **Second project phase:** fully integrated low-cost receiver with
 - single-chip receiver: LNA, BBA, down- and D/A-conversion
 - phased array with phase shifting LO
 - dual-polarization and independent steering
 - full-scale array and system demonstration



Thank you for your attention

